

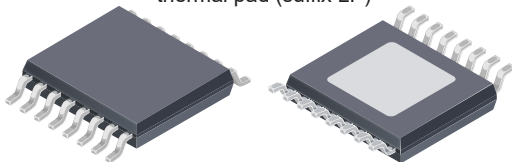
Wide Input Voltage Range, High Efficiency Fault Tolerant LED Driver

FEATURES AND BENEFITS

- Wide input voltage range: 5 to 40 V
- Maximum LED current of 120 mA
- TSSOP-16 (LP) package; exposed pad offers best-in-class thermal performance
- Typical LED accuracy of 0.5%, and 0.5% for LED-to-LED matching
- Internal bias supply for single-supply operation (typically between $V_{IN} = 8$ to 24 V)
- Integrated boost converter with 60 V DMOS switch with overvoltage protection (OVP)
- Drives up to 12 series LEDs in 2 parallel strings
- Single EN/PWM pin interface for both PWM dimming and enable function
- Sync function to synchronize boost converter switching frequencies up to 2.3 MHz, this gives the designer the ability to minimize component size
- Provides driver for external PMOS input disconnect switch
- Protection features:
 - Open or shorted V_{LED} pin protection
 - Open Schottky protection
 - Cycle-by-cycle current limit
 - Overtemperature protection (OTP)
 - Output short circuit protection

PACKAGE:

16-pin TSSOP with exposed thermal pad (suffix LP)



Not to scale

DESCRIPTION

The A8515 is a multi-output white LED (WLED) driver for LCD backlighting in consumer and industrial displays. It integrates a current-mode boost converter with an internal power DMOS switch and two current sinks. The boost converter can drive up to 24 LEDs: 12 LEDs per string at 120 mA. The LED sinks can be paralleled together to achieve higher LED currents, up to 240 mA. The A8515 can operate from a single power supply, from 5 to 40 V.

PWM dimming is implemented with an external PWM input signal. The EN/PWM dimming pin is used to control the LED intensity by using pulse width modulation.

The low 720 mV regulation voltage on the LED current sources reduces power loss and improves efficiency.

The A8515 is provided in a 16-pin TSSOP package (suffix LP) with an exposed thermal pad. It is lead (Pb) free, with 100% matte-tin leadframe plating.

APPLICATIONS

- Desktop LCD flat panel displays (FPD)
- Flat panel video displays
- LCD TVs and monitors

Typical Application Diagram

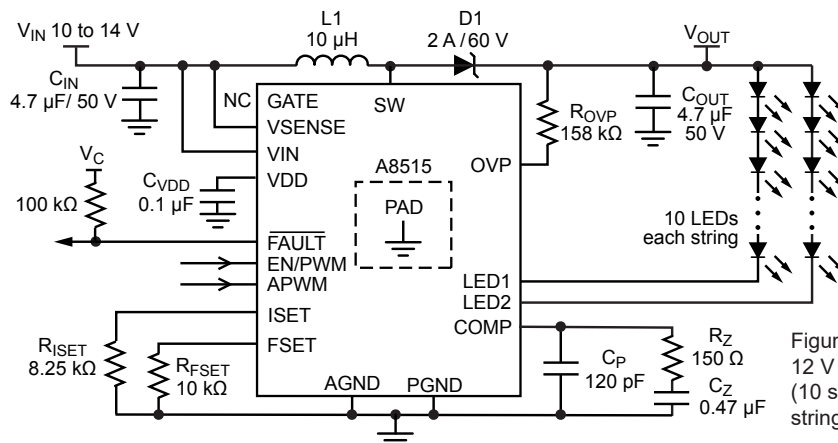


Figure 1. Typical Application Circuit; 12 V input, output to 20 LEDs (10 series LEDs in each of two strings) at 120 mA each.

A8515

Wide Input Voltage Range, High Efficiency Fault Tolerant LED Driver

SELECTION GUIDE

Part Number	Packing
A8515GLPTR-T	4000 pieces per 13-in. reel



ABSOLUTE MAXIMUM RATINGS [1]

Characteristic	Symbol	Notes	Rating	Unit
LEDx Pin			-0.3 to 55	V
OVP Pin			-0.3 to 60	V
V _{IN} , V _{SENSE} , GATE Pins		V _{SENSE} should not exceed V _{IN} by more than ±0.4 V. GATE cannot exceed V _{IN} by more than 0.4 V	-0.3 to 40	V
SW Pin		Continuous	-0.6 to 62	V
		t < 50 ns	-1.0	V
FAULT Pin			-0.3 to 40	V
ISET, FSET, APWM, COMP Pins			-0.3 to 5.5	V
All other pins			-0.3 to 7	V
Operating Ambient Temperature	T _A	Range G	-40 to 105	°C
Maximum Junction Temperature	T _{J(max)}		150	°C
Storage Temperature	T _{stg}		-55 to 150	°C

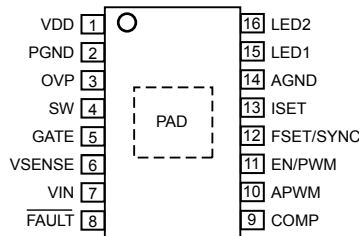
¹ Stresses beyond those listed in this table may cause permanent damage to the device. The Absolute Maximum ratings are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics table is not implied. Exposure to Absolute-Maximum-rated conditions for extended periods may affect device reliability.

THERMAL CHARACTERISTICS: May require derating at maximum conditions

Characteristic	Symbol	Test Conditions [2]	Value	Unit
Package Thermal Resistance	R _{θJA}	On 4-layer PCB based on JEDEC standard	34	°C/W
		On 2-layer PCB with 1 in. ² of copper area each side	52	°C/W

² Additional thermal information available on the Allegro website

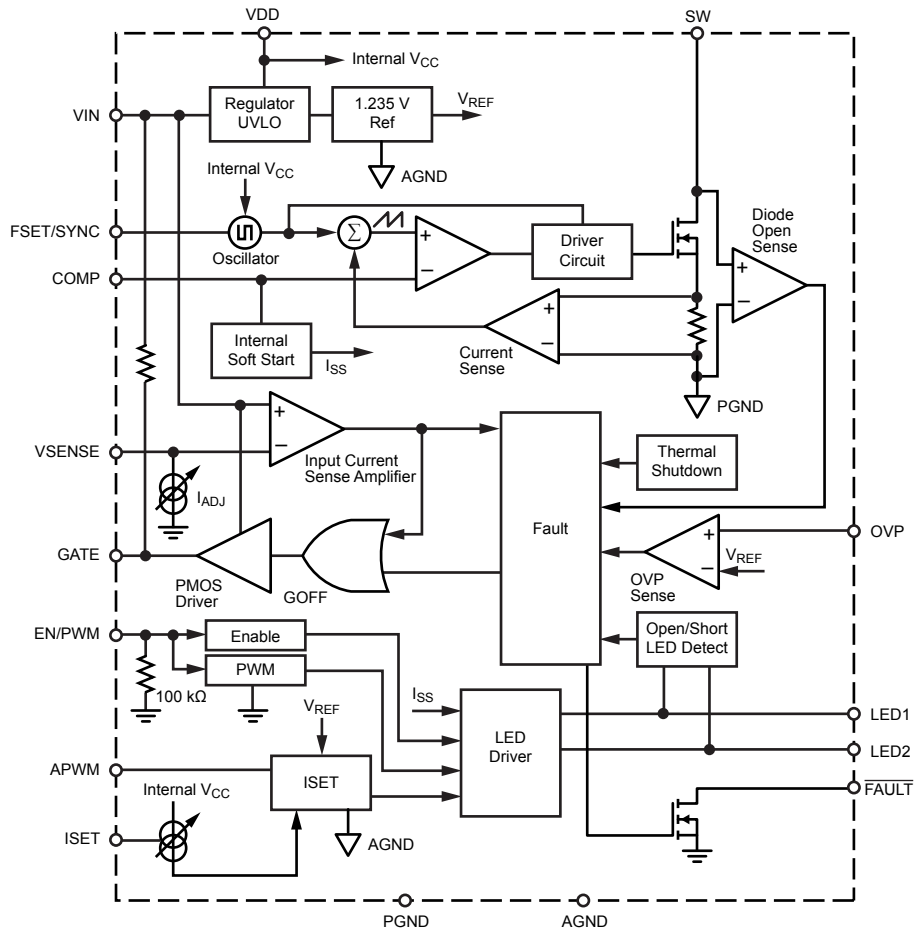
Pinout Diagram



Terminal List Table

Number	Name	Function
1	VDD	Output of internal LDO; connect a 0.1 μ F decoupling capacitor between this pin and GND.
2	PGND	Power ground for internal NMOS device.
3	OVP	This pin is used to sense an overvoltage condition; connect the R_{OVP} resistor from V_{OUT} to this pin to adjust the Overvoltage Protection function (OVP).
4	SW	The drain of the internal NMOS switch of the boost converter.
5	GATE	Output gate driver pin for external P-channel FET control.
6	VSENSE	Connect this pin to the negative sense side of the current sense resistor R_{SC} ; the threshold voltage is measured as $V_{IN} - V_{SENSE}$.
7	VIN	Input power to the A8515 as well as the positive input used for the current sense resistor.
8	FAULT	This pin is used to indicate a fault condition, it is an open drain type configuration that will be pulled low when a fault occurs; connect a 100 k Ω resistor between this pin and the required logic level voltage.
9	COMP	Output of the error amplifier and compensation node; connect a series R_ZC_Z network from this pin to GND for control loop compensation.
10	APWM	Analog trimming option or dimming; applying a digital PWM signal to this pin adjusts the internal I_{SET} current.
11	EN/PWM	PWM dimming pin used to control the LED intensity by using pulse width modulation; the typical PWM dimming frequency is in the range of 200 Hz to 1 kHz.
12	FSET/SYNC	Frequency/synchronization pin; connect a resistor R_{FSET} from this pin to GND to set the switching frequency. This pin can also be used to synchronize two or more converters in the system; the maximum synchronization frequency is 2.3 MHz.
13	ISET	Connect the R_{ISET} resistor between this pin and GND to set the LED 100% current level.
14	AGND	LED signal ground.
15	LED1	Connect the cathode of the LED string to this pin.
16	LED2	Connect the cathode of the LED string to this pin.
-	PAD	Exposed pad of the package providing enhanced thermal dissipation; this pad must be connected to the ground plane(s) of the PCB with at least 8 thermal vias, directly in the pad.

Functional Block Diagram



ELECTRICAL CHARACTERISTICS [1]: Valid at $V_{IN} = 16\text{ V}$, $T_A = 25^\circ\text{C}$, • indicates specifications guaranteed by design and characterization over the full operating temperature range with $T_A = T_J = -40^\circ\text{C}$ to 105°C , unless otherwise noted

Characteristics	Symbol	Test Conditions	Min.	Typ. [2]	Max.	Unit
INPUT VOLTAGE SPECIFICATIONS						
Operating Input Voltage Range [3]	V_{IN}		• 5	–	40	V
UVLO Start Threshold	$V_{UVLOrise}$	V_{IN} rising	• –	–	4.35	V
UVLO Stop Threshold	$V_{UVLOfall}$	V_{IN} falling	• –	–	3.90	V
UVLO Hysteresis [4]	$V_{UVLOHYS}$		–	450	–	mV
INPUT CURRENTS						
Input Quiescent Current	I_Q	EN/PWM = V_{IH} ; SW = 2 MHz, no load	–	5.5	–	mA
Input Sleep Supply Current	I_{QSLEEP}	$V_{IN} = 16\text{ V}$, EN/PWM = SYNC = 0 V	–	2	10.0	μA
INPUT LOGIC LEVELS (EN/PWM, APWM)						
Input Logic Level-Low	V_{IL}	V_{IN} throughout operating input voltage range	–	–	400	mV
Input Logic Level-High	V_{IH}	V_{IN} throughout operating input voltage range	1.5	–	–	V
EN/PWM Pin Open Drain Pull-Down Resistor	R_{ENPWM}		–	100	–	k Ω
APWM Pull-Down Resistor	R_{APWM}	EN/PWM = V_{IH}	–	100	–	k Ω
APWM						
APWM Frequency	f_{APWM}	APWM, $V_{IH} = 1.5\text{ V}$, $V_{IL} = 0.4\text{ V}$	20	–	1000	kHz
ERROR AMPLIFIER						
Open Loop Voltage Gain	A_{VOL}		–	48	–	dB
Transconductance	g_m	$\Delta I_{COMP} = \pm 10\ \mu\text{A}$	–	990	–	$\mu\text{A/V}$
Source Current	$I_{EA(SRC)}$	$V_{COMP} = 1.5\text{ V}$	–	–350	–	μA
Sink Current	$I_{EA(SINK)}$	$V_{COMP} = 1.5\text{ V}$	–	350	–	μA
COMP Pin Pull-Down Resistance	R_{COMP}	FAULT = 1	–	2000	–	Ω
OVERVOLTAGE PROTECTION						
Overvoltage Threshold	$V_{OVP(th)}$	OVP connected to V_{OUT}	7.7	8.1	8.5	V
OVP Sense Current	I_{OVPH}		188	199	210	μA
OVP Leakage Current	I_{OVPLKG}	$R_{OVP} = 40.2\text{ k}\Omega$, $V_{IN} = 16\text{ V}$, EN/PWM = V_{IL}	–	0.1	1	μA
Secondary Overvoltage Protection	$V_{OVP(sec)}$		–	55	–	V
BOOST SWITCH						
Switch On-Resistance	R_{SW}	$I_{SW} = 0.750\text{ A}$, $V_{IN} = 16\text{ V}$	–	300	–	m Ω
Switch Leakage Current	I_{SWLKG}	$V_{SW} = 16\text{ V}$, EN/PWM = V_{IL}	–	0.1	1	μA
Switch Current Limit	$I_{SW(LIM)}$		3.0	3.5	4.2	A
Secondary Switch Current Limit [4]	$I_{SW(LIM2)}$	Higher than $I_{SW(LIM)}(\text{max})$ for all conditions, device latches when detected	–	7	–	A
Soft Start Boost Current Limit	$I_{SWSS(LIM)}$	Initial soft start current for boost switch	–	700	–	mA
Minimum Switch On-Time	$t_{SWONTIME}$		–	85	–	ns
Minimum Switch Off-Time	$t_{SWOFFTIME}$		–	47	–	ns

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ELECTRICAL CHARACTERISTICS [1] (continued): Valid at $V_{IN} = 16\text{ V}$, $T_A = 25^\circ\text{C}$, • indicates specifications guaranteed by design and characterization over the full operating temperature range with $T_A = T_J = -40^\circ\text{C}$ to 105°C , unless otherwise noted

Characteristics	Symbol	Test Conditions	Min.	Typ. [2]	Max.	Unit
OSCILLATOR FREQUENCY						
Oscillator Frequency	f_{SW}	$R_{FSET} = 10\text{ k}\Omega$	• 1.8	2	2.2	MHz
		$R_{FSET} = 20\text{ k}\Omega$	–	1	–	MHz
		$R_{FSET} = 35.6\text{ k}\Omega$	–	580	–	kHz
FSET/SYNC Pin Voltage	V_{FSET}	$R_{FSET} = 10\text{ k}\Omega$	–	1.00	–	V
FSET Frequency Range	f_{FSET}		580	–	2500	kHz
SYNCHRONIZATION						
Synchronized PWM Frequency	f_{SWSYNC}		580	–	2300	kHz
Synchronization Input Minimum Off-Time	$t_{PWSYNCOFF}$		150	–	–	ns
Synchronization Input Minimum On-Time	$t_{PWSYNCON}$		150	–	–	ns
SYNC Input Logic Voltage	$V_{SYNC(H)}$	FSET/SYNC pin, high level	• 2.0	–	–	V
	$V_{SYNC(L)}$	FSET/SYNC pin, low level	• –	–	0.4	V
LED CURRENT SINKS						
LEDx Accuracy	Err_{LED}	$I_{SET} = 120\text{ }\mu\text{A}$	• –	0.5	2	%
LEDx Matching	$\Delta LEDx$	$I_{SET} = 120\text{ }\mu\text{A}$	• –	0.5	1	%
LEDx Regulation Voltage	V_{LED}	$V_{LED1} = V_{LED2}$, $I_{SET} = 120\text{ }\mu\text{A}$	–	720	–	mV
I_{SET} to I_{LEDx} Current Gain	A_{ISET}	$I_{SET} = 120\text{ }\mu\text{A}$	• 960	980	1000	A/A
ISET Pin Voltage	V_{ISET}		–	1.003	–	V
Allowable ISET Current	I_{SET}		• 40	–	125	μA
V_{LED} Short Detect	V_{LEDDSC}	While LED sinks are in regulation, sensed from LEDx pin to GND	4.6	–	–	V
Soft Start LEDx Current	I_{LEDSS}	Current through each enabled LEDx pin during soft start	–	3.2	–	mA
Maximum PWM Dimming Until Off-Time	t_{PWML}	Measured while EN/PWM = low, during dimming control and internal references are powered-on (exceeding t_{PWML} results in shutdown)	–	32,750	–	f_{SW} cycles
Minimum PWM On-Time	t_{PWMH}	First cycle when powering-up device	–	0.75	2	μs
EN/PWM High to LED-On Delay	$t_{dPWM(on)}$	Time between PWM enable and LED current reaching 90% of maximum	–	0.5	1	μs
EN/PWM Low to LED-Off Delay	$t_{dPWM(off)}$	Time between PWM enable going low and LED current reaching 10% of maximum	–	–	500	ns
GATE PIN						
Gate Pin Sink Current	I_{GSINK}	$V_{GS} = 0\text{ V}$ with respect to V_{IN}	–	–104	–	μA
Gate Fault Shutdown	t_{GFAULT}		–	–	3	μs
Gate Voltage	V_{GS}	Gate to source voltage measured when gate is on	–	–6.7	–	V

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ELECTRICAL CHARACTERISTICS [1] (continued): Valid at $V_{IN} = 16\text{ V}$, $T_A = 25^\circ\text{C}$, • indicates specifications guaranteed by design and characterization over the full operating temperature range with $T_A = T_J = -40^\circ\text{C}$ to 105°C , unless otherwise noted

Characteristics	Symbol	Test Conditions	Min.	Typ. [2]	Max.	Unit
VSENSE PIN						
VSENSE Pin Sink Current	I_{ADJ}		18.8	20.3	21.8	μA
VSENSE Trip Point	$V_{SENSE\text{trip}}$	Measured between VIN and VSENSE, $R_{ADJ} = 0\ \Omega$	–	180	–	mV
FAULT PIN						
$\overline{\text{FAULT}}$ Pull-Down Voltage	V_{FAULT}	$I_{\text{FAULT}} = 1\text{ mA}$ (400 Ω)	–	–	0.5	V
$\overline{\text{FAULT}}$ Pin Leakage Current	I_{FAULTLK}	$V_{\text{FAULT}} = 5\text{ V}$	–	–	1	μA
THERMAL PROTECTION (TSD)						
Thermal Shutdown Threshold [4]	T_{SD}	Temperature rising	–	165	–	$^\circ\text{C}$
Thermal Shutdown Hysteresis [4]	T_{SDHYS}		–	20	–	$^\circ\text{C}$

¹ For input and output current specifications, negative current is defined as coming out of the node or pin (sourcing); positive current is defined as going into the node or pin (sinking).

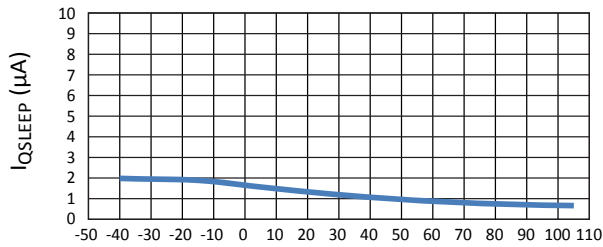
² Typical specifications are at $T_A = 25^\circ\text{C}$.

³ Minimum $V_{IN} = 5\text{ V}$ is only required at startup. After startup is completed, the IC is able to function down to $V_{IN} = 4\text{ V}$.

⁴ Ensured by design and characterization, not production tested.

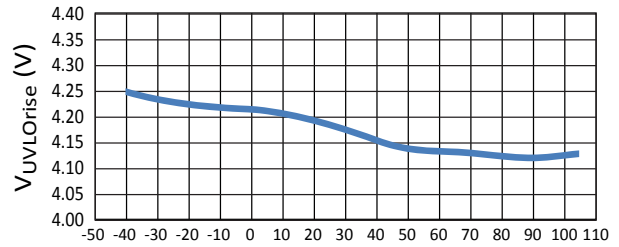
CHARACTERISTIC PERFORMANCE

**VIN Input Sleep Mode Current
versus Ambient Temperature**



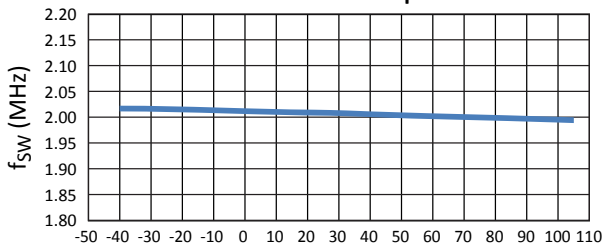
Temperature (°C)

**VIN UVLO Start Threshold Voltage
versus Ambient Temperature**



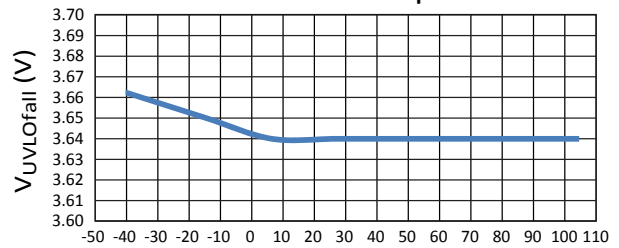
Temperature (°C)

**Switching Frequency
versus Ambient Temperature**



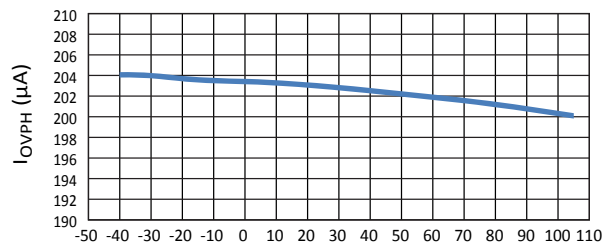
Temperature (°C)

**VIN UVLO Stop Threshold Voltage
versus Ambient Temperature**



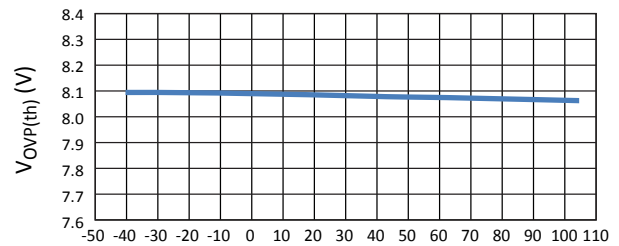
Temperature (°C)

**OVP Pin Sense Current
versus Ambient Temperature**



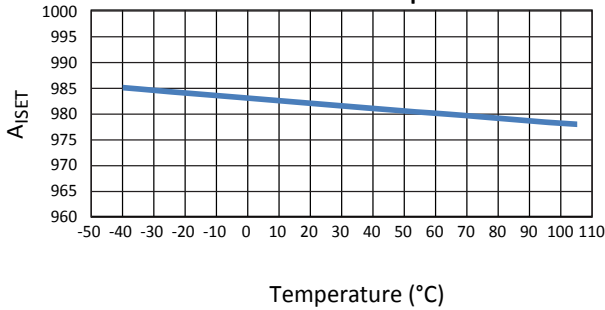
Temperature (°C)

**OVP Pin Overvoltage Threshold
versus Ambient Temperature**

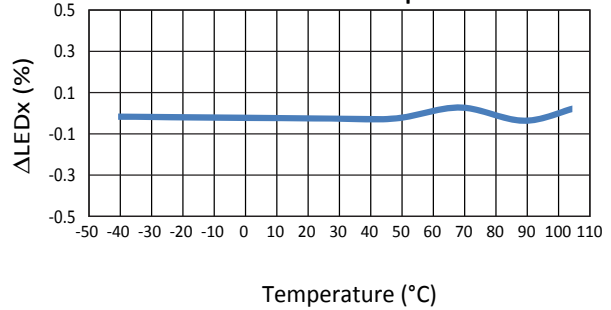


Temperature (°C)

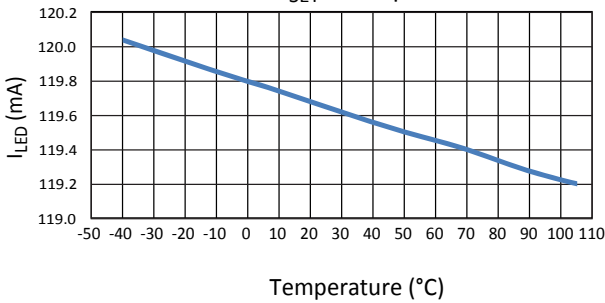
**ISET to LED Current Gain
versus Ambient Temperature**



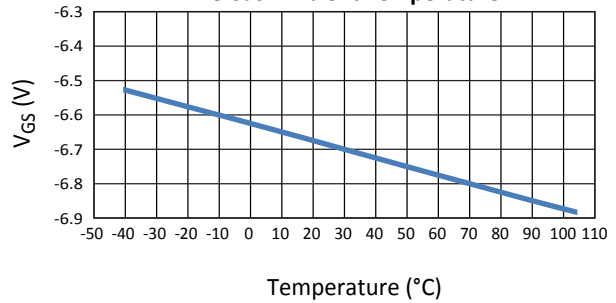
**LED to LED Matching Accuracy
versus Ambient Temperature**



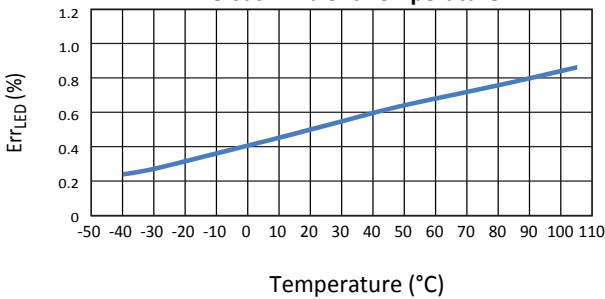
**LED Current versus Ambient Temperature
I_{SET} = 120 μA**



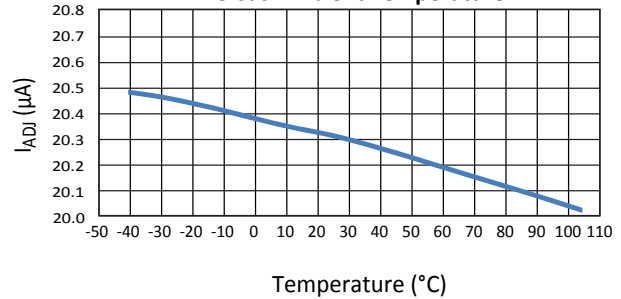
**Input Disconnect Switch Gate to Source Voltage
versus Ambient Temperature**



**LED Current Setpoint Accuracy
versus Ambient Temperature**

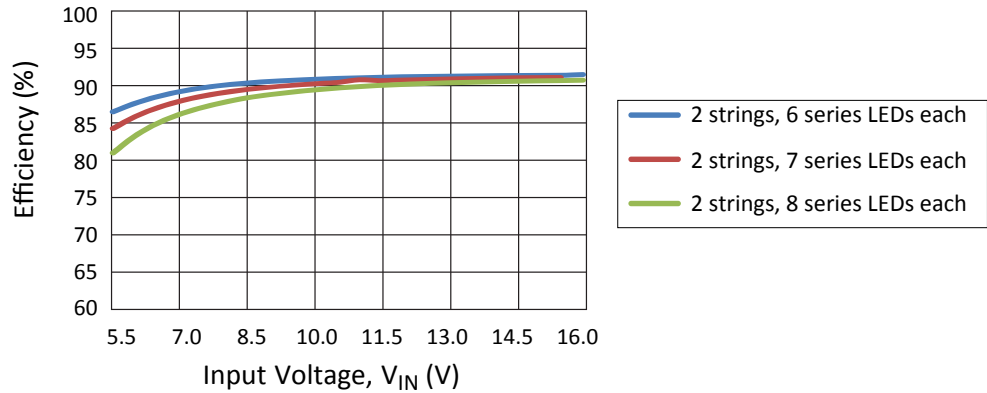


**VSENSE Pin Sink Current
versus Ambient Temperature**



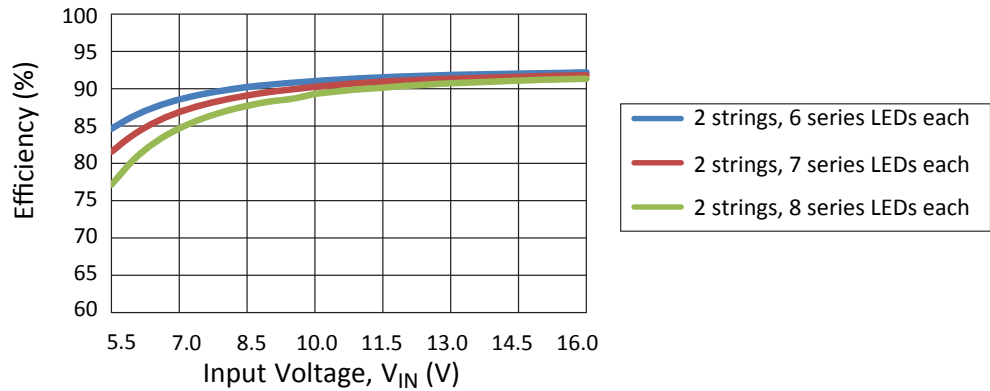
Efficiency for Various LED Configurations

$I_{LED} = 80 \text{ mA}$, LED $V_f \approx 3.2 \text{ V}$



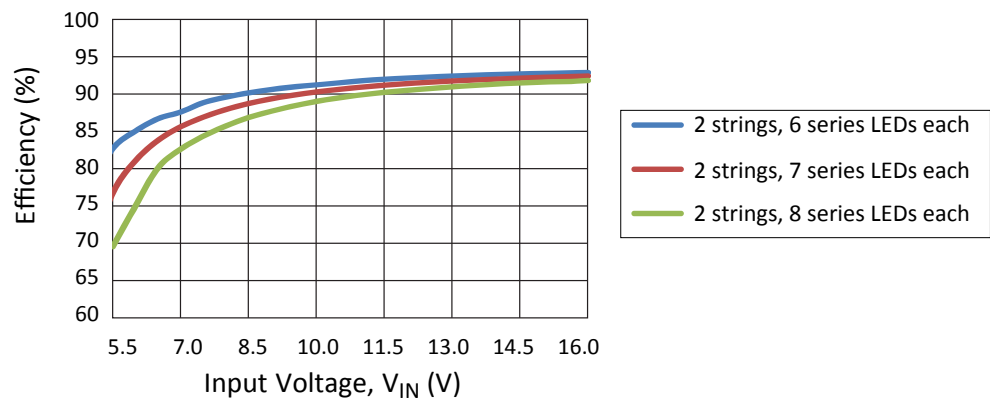
Efficiency for Various LED Configurations

$I_{LED} = 100 \text{ mA}$, LED $V_f \approx 3.2 \text{ V}$



Efficiency for Various LED Configurations

$I_{LED} = 120 \text{ mA}$, LED $V_f \approx 3.2 \text{ V}$



FUNCTIONAL DESCRIPTION

The A8515 incorporates a current-mode boost controller with internal DMOS switch, and two LED current sinks. It can be used to drive two LED strings of up to 12 white LEDs in series, with current up to 120 mA per string. For optimal efficiency, the output of the boost stage is adaptively adjusted to the minimum voltage required by both LED strings. This is expressed by the following equation:

$$V_{OUT} = \max(V_{LED1}, V_{LED2}) + V_{REG} \quad (1)$$

where

V_{LEDx} is the voltage drop across LED string 1 and 2, and

V_{REG} is the regulation voltage of the LED current sinks (typically 0.72 V at the maximum LED current).

ENABLING THE IC

The IC turns on when a logic high signal is applied on the EN/PWM pin with a minimum duration of t_{PWMH} for the first clock cycle, and the input voltage present on the VIN pin is greater than the 4.35 V necessary to clear the UVLO ($V_{UVLOrise}$) threshold. The power-up sequence is shown in figure 2. Before the LEDs are enabled, the A8515 driver goes through a system check to determine if there are any possible fault conditions that might prevent the system from functioning correctly. Also, if the FSET pin is pulled low, the IC will not power-up. More information on the FSET pin can be found in the Sync section of this datasheet.

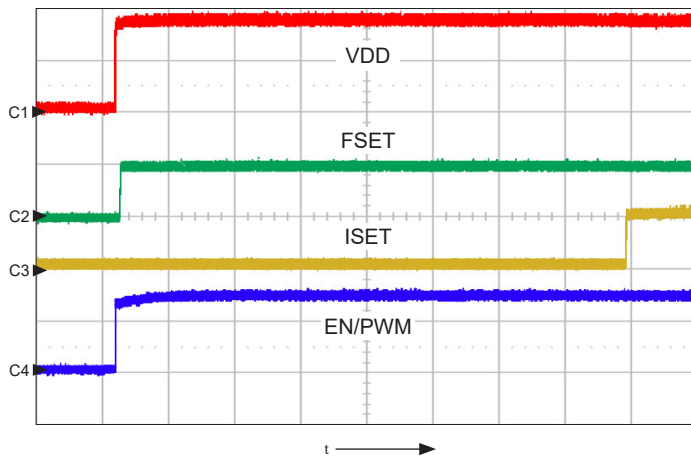


Figure 2. Power-up diagram; shows VDD (ch1, 2 V/div.), FSET (ch2, 1 V/div.), ISET (ch3, 1 V/div.), and EN/PWM (ch4, 2 V/div.) pins, 200 μ s/div.

POWERING UP: LED PIN SHORT-TO-GND CHECK

The VIN pin has a UVLO function that prevents the A8515 from powering-up until the UVLO threshold is reached. After the VIN pin goes above UVLO, and a high signal is present on the EN/PWM pin, the IC proceeds to power-up. As shown in figure 3, at this point the A8515 enables the disconnect switch and checks if any LED pins are shorted to GND and/or are not used. If an LEDx pin is shorted to ground the A8515 will not proceed with soft start until the short is removed from the LEDx pin. This prevents the A8515 from powering-up and putting an uncontrolled amount of current through the LEDs. The various detect scenarios are presented on the next page, in figures 4A to 4C.

The LED detect phase starts when the GATE voltage of the disconnect switch is equal to $V_{IN} - 4.5$ V. After the voltage threshold on the LEDx pins exceeds 120 mV, a delay of between 3000 and 4000 clock cycles is used to determine the status of the pins. Thus, the LED detection duration varies with the switching frequency, as shown in the following table:

Switching Frequency (MHz)	Detection Time (ms)
2	1.5 to 2
1	3 to 4
0.800	3.75 to 5
0.600	5 to 6.7

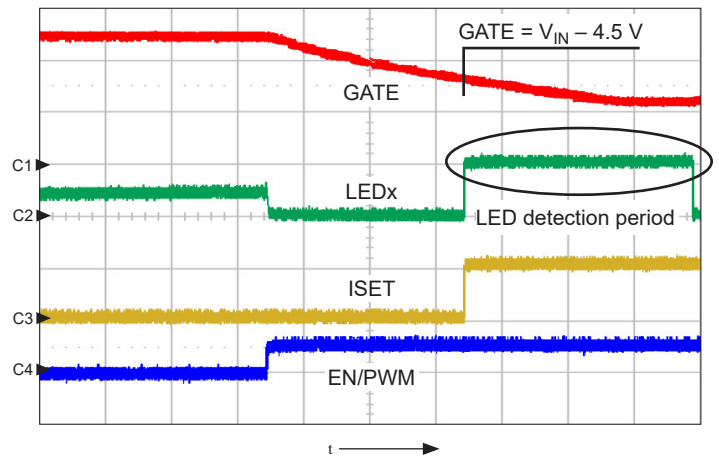


Figure 3. Power-up diagram; shows the relationship of an LEDx pin with respect to the gate voltage of the disconnect switch (if used) during the LED detect phase, as well as the duration of the LED detect phase for a switching frequency of 2 MHz; shows GATE (ch1, 5 V/div.), ILED (ch2, 500 mV/div.), ISET (ch3, 1 V/div.), and EN/PWM (ch4, 5 V/div.) pins, 500 μ s/div.

The LED pin detection voltage thresholds are as follows:

LED Pin Voltage	LED Pin Status	Action
<70 mV	Short-to-GND	Power-up is halted
150 mV	Not used	LED removed from operation
>325 mV	LED pin in use	None

All unused pins should be connected with a 1.54 kΩ resistor to GND, as shown in figure 5. The unused pin, with the pull-down resistor, will be taken out of regulation at this point and will not contribute to the boost regulation loop.

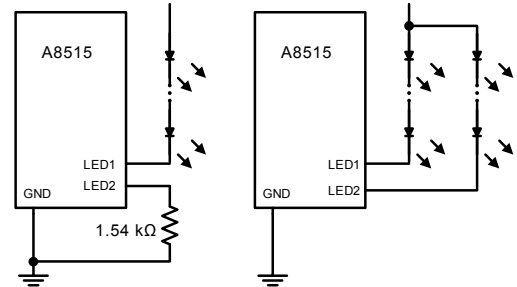
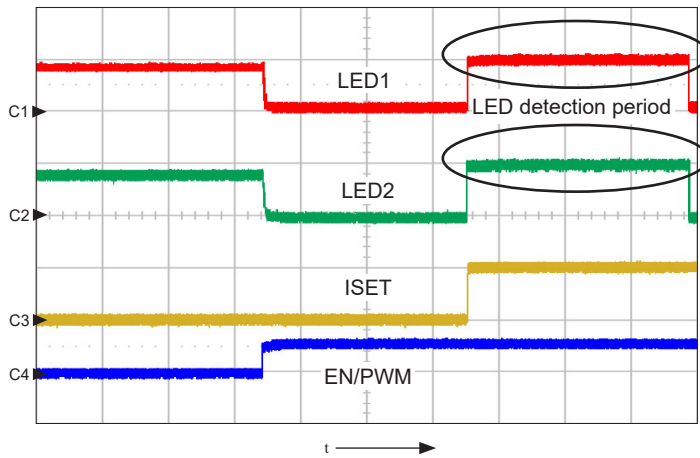
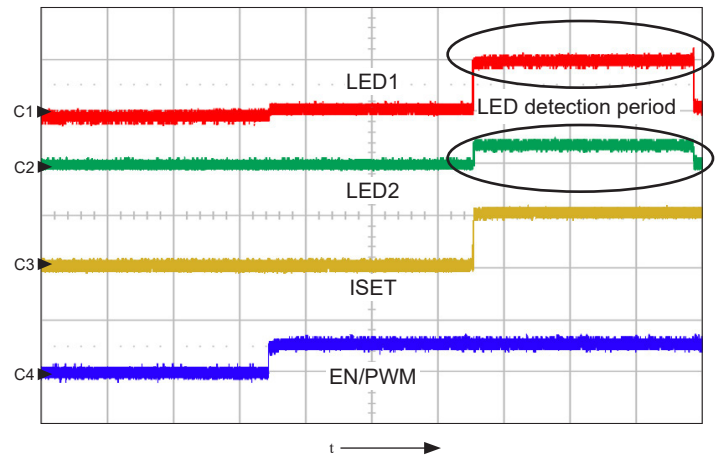


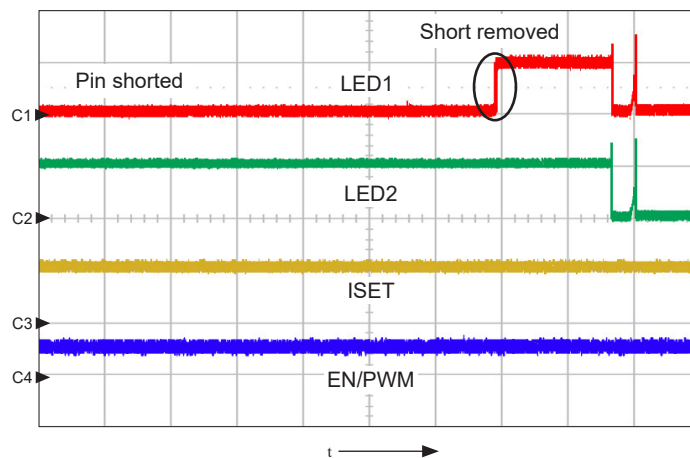
Figure 5. Channel select setup: (left) using only channel LED1, (right) using both channels.



4A. An LED detect occurring when both LED pins are selected to be used; shows LED1 (ch1, 500 mV/div.), LED2 (ch2, 500 mV/div.), ISET (ch3, 1 V/div.), and EN/PWM (ch4, 5 V/div.) pins, 500 μs/div.



4B. Example with LED2 pin not being used; the detect voltage is about 150 mV; shows LED1 (ch1, 500 mV/div.), LED2 (ch2, 500 mV/div.), ISET (ch3, 1 V/div.), and EN/PWM (ch4, 5 V/div.) pins, 500 μs/div.



4C. Example with one LED shorted to GND. The IC will not proceed with power-up until the shorted LED pin is released, at which point the LED is checked to see if it is being used; shows LED1 (ch1, 500 mV/div.), LED2 (ch2, 500 mV/div.), ISET (ch3, 1 V/div.), and EN/PWM (ch4, 5 V/div.) pins, 1 ms/div.

SOFT START FUNCTION

During soft start the LEDx pins are set to sink (I_{LEDSS}) and the boost switch current is reduced to the $I_{SWSS(LIM)}$ level to limit the inrush current generated by charging the output capacitors. When the converter senses that there is enough voltage on the LED pins the converter proceeds to increase the LED current to the preset regulation current and the boost switch current limit is switched to the $I_{SW(LIM)}$ level to allow the A8515 to deliver the necessary output power to the LEDs. This is shown in figure 7.

FREQUENCY SELECTION

The switching frequency on the boost regulator is set by the resistor connected to the FSET pin, and the switching frequency can be anywhere from 580 kHz to 2.3 MHz. Figure 6 shows the typical switching frequencies, in MHz, for given resistor values, in k Ω .

If during operation a fault occurs that will increase the switching frequency, the FSET pin is clamped to a maximum switching frequency of no more than 3.5 MHz. If the FSET pin is shorted to GND the part will shut down. For more details see the Fault Mode table later in this section.

SYNC

The A8515 can also be synchronized using an external clock on the SYNC pin. Figure 8 shows the correspondence of a sync signal and the FSET pin, and figure 9 shows the result when a sync signal is detected: the LED current does not show any variation while the frequency changeover occurs. At power-up if the FSET pin is held low, the IC will not power-up. Only when the FSET pin is tri-stated to allow for the pin to rise, to about 1 V, or when a sync clock is detected, will the A8515 try to power-up.

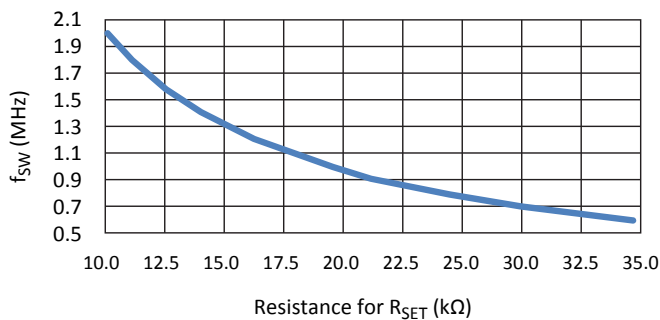


Figure 6. Typical Switching Frequency versus value of R_{FSET} resistor.

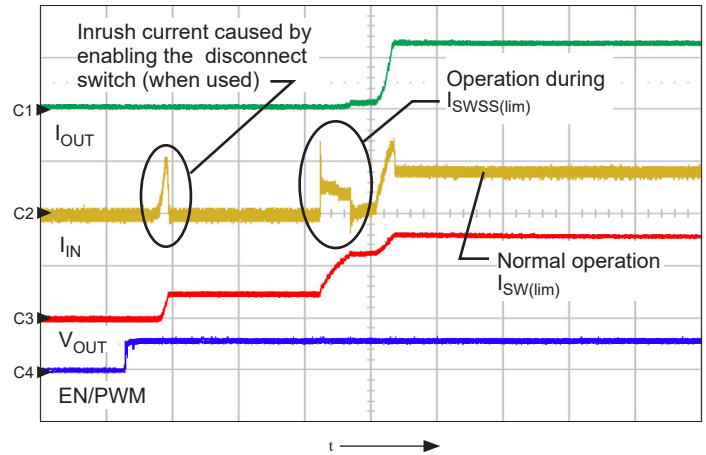


Figure 7. Startup diagram showing the input current, output voltage, and output current; shows I_{OUT} (ch1, 200 mA/div.), I_{IN} (ch2, 1 A/div.), V_{OUT} (ch3, 20 V/div.), and EN/PWM (ch4, 5 V/div.), 1 ms/div.

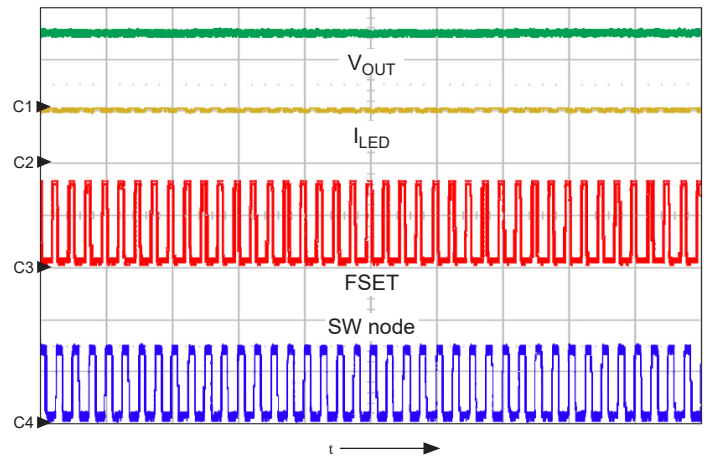


Figure 8. Diagram showing a synchronized FSET pin and switch node; shows V_{OUT} (ch1, 20 V/div.), I_{LED} (ch2, 200 mA/div.), FSET (ch3, 2 V/div.), and SW node (ch4, 20 V/div.), 2 μ s/div.

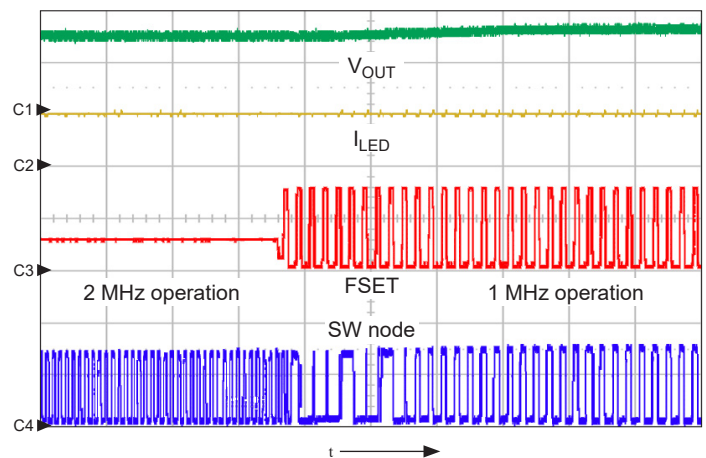


Figure 9. Transition of the SW waveform when the SYNC pulse is detected. The A8515 switching at 2 MHz, applied SYNC pulse at 1 MHz; shows V_{OUT} (ch1, 20 V/div.), I_{LED} (ch2, 200 mA/div.), FSET (ch3, 2 V/div.), and SW node (ch4, 20 V/div.), 5 μ s/div.

The basic requirement of the sync signal is 150 ns minimum on-time and 150 ns minimum off time, as indicated by the specifications for $t_{PWSYNCON}$ and $t_{PWSYNCOFF}$. Figure 9 shows the timing for a synchronization clock into the A8515 at 2.2 MHz. Thus, any pulse with a duty cycle of 33% to 66% at 2.2 MHz can be used to synchronize the IC. The rise and fall edges should be about 10 ns.

The SYNC pulse duty cycle ranges for selected switching frequencies are:

SYNC Pulse Frequency (MHz)	Duty Cycle Range (%)
2.2	33 to 66
2	30 to 70
1	15 to 85
0.800	12 to 88
0.600	9 to 91

If during operation a sync clock is lost, the IC will revert to the preset switching frequency that is set by the resistor R_{FSET} . During this period the IC will stop switching for a maximum period of about 7 μ s to allow the sync detection circuitry to switch over to the externally preset switching frequency. If the clock is held low for more than 7 μ s, the A8515 will shut down. In this shutdown mode the IC will stop switching, the input disconnect switch is open, and the LEDs will stop sinking current. To shut-down the IC into low power mode, the user needs to disable the IC using the EN/PWM pin, by keeping the pin low for a period of 65 ms. If the FSET pin is released at any time after 5 μ s, the A8515 will proceed to soft start.

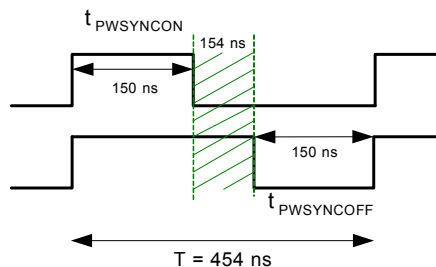


Figure 10. SYNC pulse on and off time requirements.

LED CURRENT SETTING AND LED DIMMING

The maximum LED current can be up to 120 mA per channel and is set through the ISET pin. To set the I_{LED} current, connect a resistor, R_{ISET} , between this pin and GND, according to the following formula:

$$R_{ISET} = 980 / I_{LED} \quad (2)$$

where I_{LED} is in A and R_{ISET} is in Ω . This sets the maximum current through the LEDs, referred to as the *100% current*. Standard R_{ISET} values, at gain equals 980, are as follows:

Standard Closest R_{ISET} Resistor Value (k Ω)	LED current per LED, I_{LED} (mA)
8.25	120
9.76	100
12.1	80
15.0	65

PWM DIMMING

The LED current can be reduced from the 100% current level by PWM dimming using the EN/PWM pin. When the EN/PWM pin is pulled high, the A8515 turns on and all enabled LEDs sink 100% current. When EN/PWM is pulled low, the boost converter and LED sinks are turned off. The compensation (COMP) pin is floated, and critical internal circuits are kept active. The typical PWM dimming frequencies fall between 200 Hz and 1 kHz. Figures 12A to 12D provide examples of PWM switching behavior.

Another important feature of the A8515 is the PWM signal to LED current delay. This delay is typically less than 500 ns, which allows greater accuracy at low PWM dimming duty cycles, as shown in figure 11.

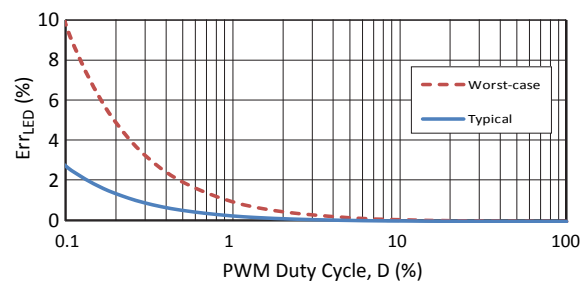


Figure 11. Percentage Error of the LED current versus PWM duty cycle (at 200 Hz PWM frequency).

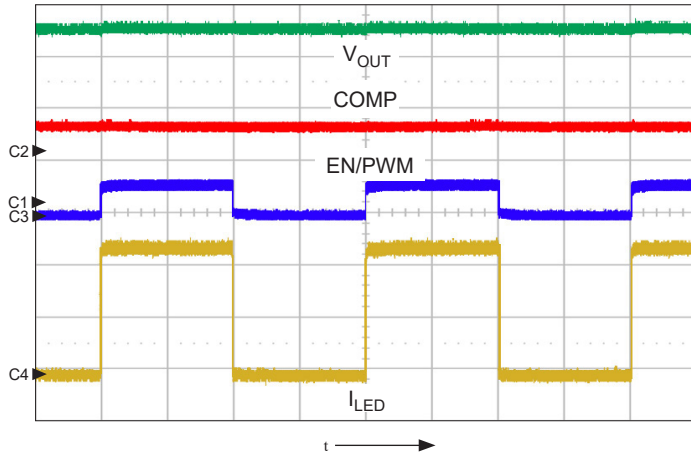


Figure 12A. Typical PWM diagram showing V_{OUT} , I_{LED} , and COMP pin as well as the EN/PWM signal. PWM dimming frequency is 500 Hz at 50% duty cycle; shows V_{OUT} (ch1, 10 V/div.), COMP (ch2, 2 V/div.), EN/PWM (ch3, 5 V/div.), and I_{LED} (ch4, 100 mA/div.), 500 μ s/div.

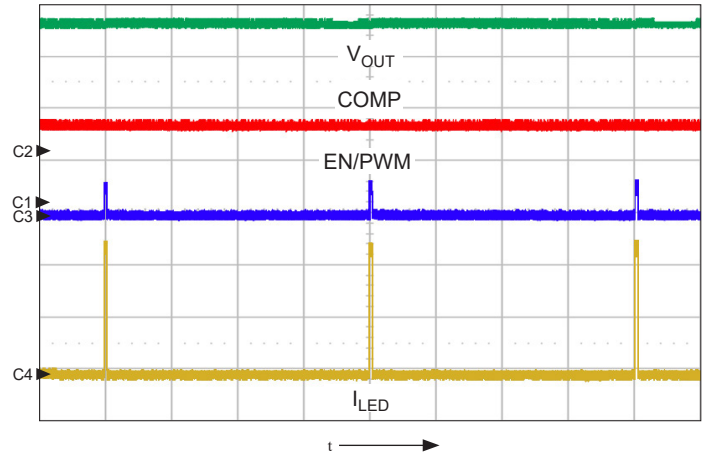


Figure 12B. Typical PWM diagram showing V_{OUT} , I_{LED} , and COMP pin as well as the EN/PWM signal. PWM dimming frequency is 500 Hz at 1% duty cycle ; shows V_{OUT} (ch1, 10 V/div.), COMP (ch2, 2 V/div.), EN/PWM (ch3, 5 V/div.), and I_{LED} (ch4, 100 mA/div.), 500 μ s/div.

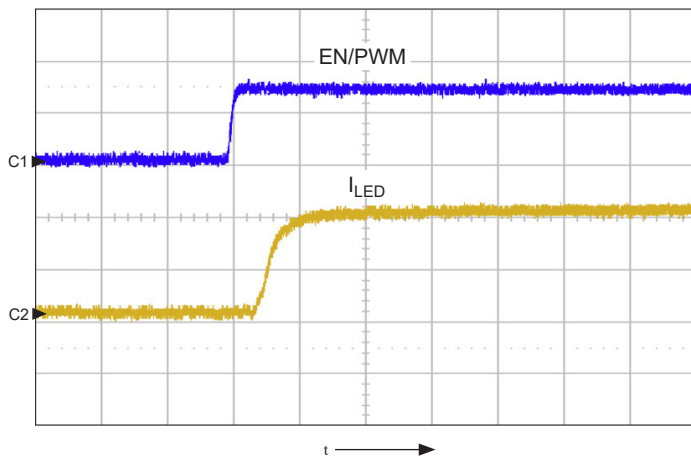


Figure 12C. Delay from rising edge of EN/PWM signal to LED current; shows EN/PWM (ch1, 2 V/div.), and I_{LED} (ch2, 50 mA/div.), 200 ns/div.

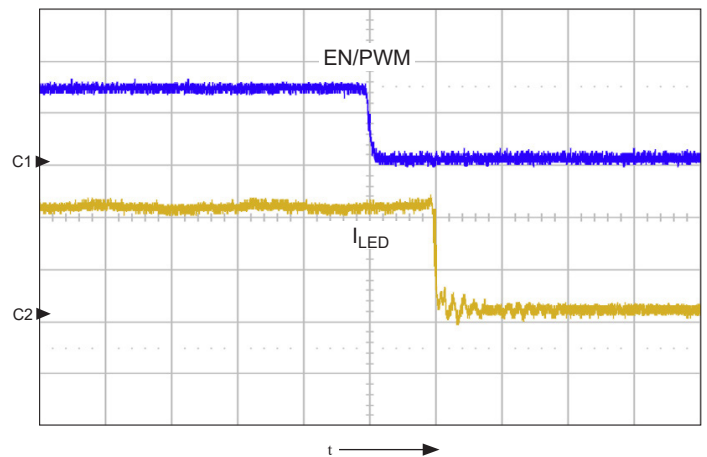


Figure 12D. Delay from falling edge of EN/PWM signal to LED current turn off; shows EN/PWM (ch1, 2 V/div.), and I_{LED} (ch2, 50 mA/div.), 200 ns/div.

APWM PIN

The APWM pin is used in conjunction with the ISET pin. This is a digital signal pin that internally adjusts the ISET current. The typical input signal frequency is between 20 kHz and 1 MHz. The duty cycle of this signal is inversely proportional to the percentage of current that is delivered to the LEDs (figure 14). As an example, a system that delivers a full LED current of 120 mA per LED would deliver 90 mA of current per LED when an APWM signal is applied with a duty cycle of 25%. When this pin is not used it should be tied to GND.

To use this pin for a trim function, the user should set the maximum output current to a value higher than the required current by at least 5%. The LED ISET current is then trimmed down to the

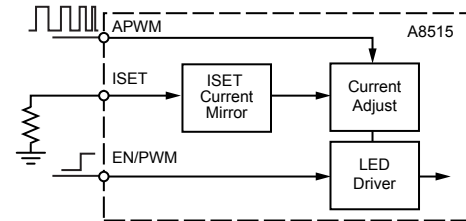


Figure 13. Simplified block diagram of the APWM ISET block.

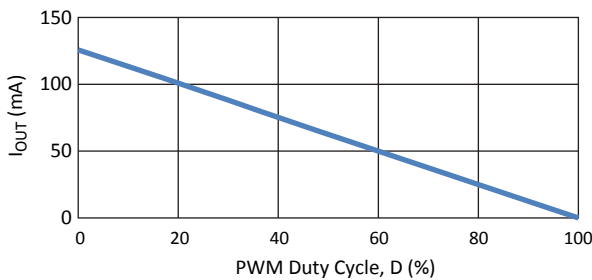


Figure 14. Output current versus duty cycle; 200 kHz APWM signal.

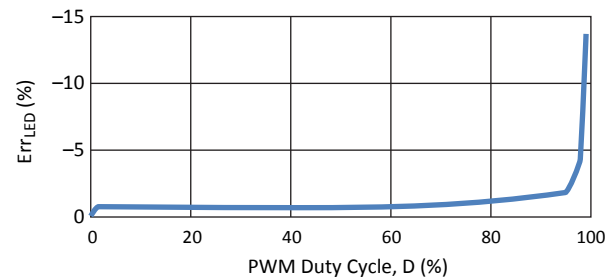


Figure 15. Percentage Error of the LED current versus PWM duty cycle; 200 kHz APWM signal.

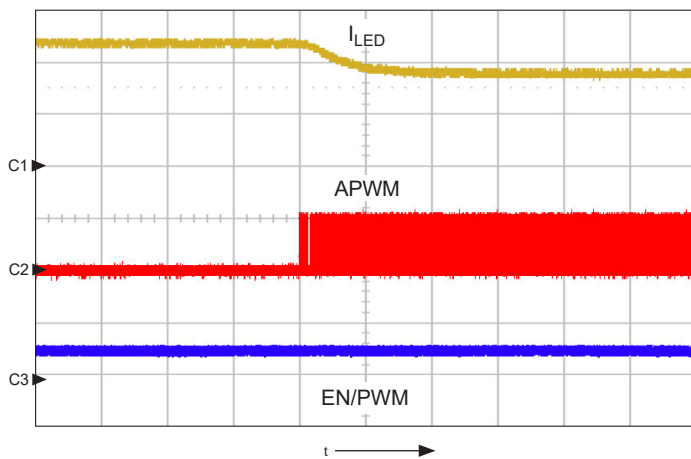


Figure 16. Diagram showing the transition of LED current from 120 mA to 90 mA, when a 25% duty cycle signal is applied to the APWM pin; EN/PWM = 1; shows I_{LED} (ch1, 50 mA/div.), APWM (ch2, 5 V/div.), and EN/PWM (ch3, 5 V/div.), 500 μs/div.

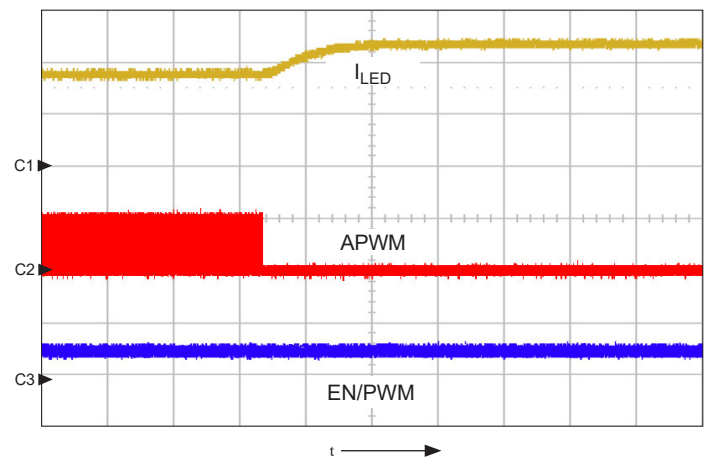


Figure 17. Diagram showing the transition of LED current from 90 mA to 120 mA, when a 25% duty cycle signal is removed from the APWM pin. EN/PWM = 1; shows I_{LED} (ch1, 50 mA/div.), APWM (ch2, 5 V/div.), and EN/PWM (ch3, 5 V/div.), 500 μs/div.

appropriate value. Another consideration that also is important is the limitation of the user APWM signal duty cycle. In some cases, it might be preferable to set the maximum ISET current to be 25% to 50% higher, thus allowing the APWM signal to have duty cycles that are between 25% and 50%.

Although the APWM dimming function has a wide frequency range, if this function is used strictly as an analog dimming function it is recommended to use frequency ranges between 50 and 500 kHz for best accuracy. The frequency range must be considered only if the user is not using this function as a closed loop trim function. Another limitation is that the propagation delay between this APWM signal and I_{OUT} takes several milliseconds to change the actual LED current. This effect is shown in figures 16 through 18.

ANALOG DIMMING

The A8515 can also be dimmed by using an external DAC or another voltage source applied either directly to the ground side of the R_{ISET} resistor or through an external resistor to the ISET pin (see figure 19).

- For a single resistor (upper panel of figure 19), the ISET current

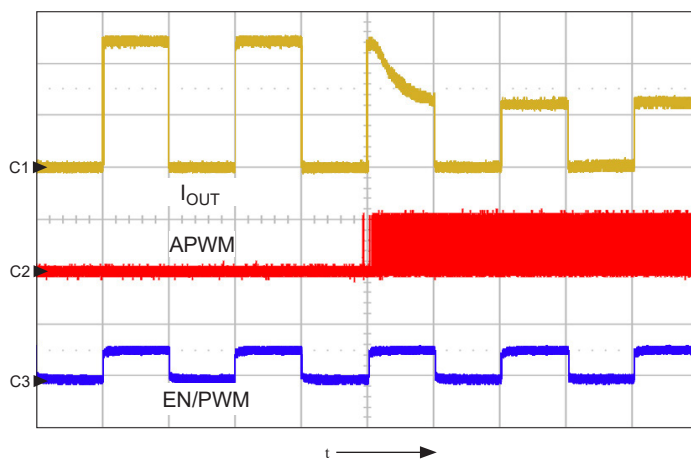


Figure 18. Transition of output current level when a 50% duty cycle signal is applied to the APWM pin, in conjunction with a 50% duty cycle PWM dimming being applied to the EN/PWM pin; shows I_{OUT} (ch1, 100 mA/div.), APWM (ch2, 5 V/div.), and EN/PWM (ch3, 5 V/div.), 1 ms/div.

is controlled by the following formula:

$$I_{SET} = \frac{V_{ISET} - V_{DAC}}{R_{ISET} - V_{DAC}} \quad (3)$$

Where V_{ISET} is the ISET pin voltage and V_{DAC} is the DAC output voltage.

When the DAC voltage is equal to V_{ISET}, the internal reference, there is no current through R_{ISET}. When the DAC voltage starts to decrease, the ISET current starts to increase, thus increasing the LED current. When the DAC voltage is 0 V, the LED current will be at its maximum.

- For a dual-resistor configuration (lower panel of figure 19), the ISET current is controlled by the following formula:

$$I_{SET} = \frac{V_{ISET}}{R_{ISET}} - \frac{V_{DAC} - V_{ISET}}{R_1} \quad (4)$$

The advantage of this circuit is that the DAC voltage can be higher or lower, thus adjusting the LED current to a higher or lower value of the preset LED current set by the R_{ISET} resistor:

- V_{DAC} = 1.003 V; the output is strictly controlled by R_{ISET}
- V_{DAC} > 1.003 V; the LED current is reduced
- V_{DAC} < 1.003 V; the LED current is increased

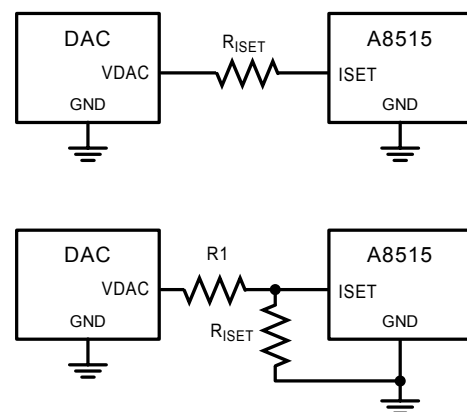


Figure 19. Simplified diagrams of voltage control of I_{LED}: typical applications using a DAC to control I_{LED} using a single resistor (upper), and dual resistors (lower).

LED SHORT DETECT

Both LEDx pins are capable of handling the maximum V_{OUT} that the converter can deliver, thus providing protection from the LED pin to V_{OUT} in the event of a connector short.

An LED pin that has a voltage exceeding V_{LEDSC} will be removed from operation (see figure 20). This is to prevent the IC from dissipating too much power by having a large voltage present on an LEDx pin.

While the IC is being PWM-dimmed, the IC rechecks the disabled LED every time the EN/PWM signal goes high, to prevent false tripping of an LED short event. This also allows some self-correction if an intermittent LED pin short-to- V_{OUT} is present.

OVERVOLTAGE PROTECTION

The A8515 has overvoltage protection (OVP) and open Schottky diode protection. The OVP protection has a default level of 8 V and can be increased up to 55 V by connecting R_{OVP} between the OVP pin and V_{OUT} . When the current into the OVP pin exceeds

199 μ A typical, the OVP comparator goes low and the boost stops switching.

The following equation can be used to determine the resistance for setting the OVP level:

$$R_{OVP} = (V_{OUTovp} - V_{OVP(th)}) / I_{OVPH} \quad (5)$$

where:

V_{OUTovp} is the target overvoltage level,

R_{OVP} is the value of the external resistor, in Ω ,

$V_{OVP(th)}$ is the pin OVP trip point found in the Electrical Characteristics table, and

I_{OVPH} is the current into the OVP pin.

There are several possibilities for why an OVP condition would be encountered during operation, the two most common being: a disconnected output, and an open LED string. Examples of these are provided in figures 21 and 22.

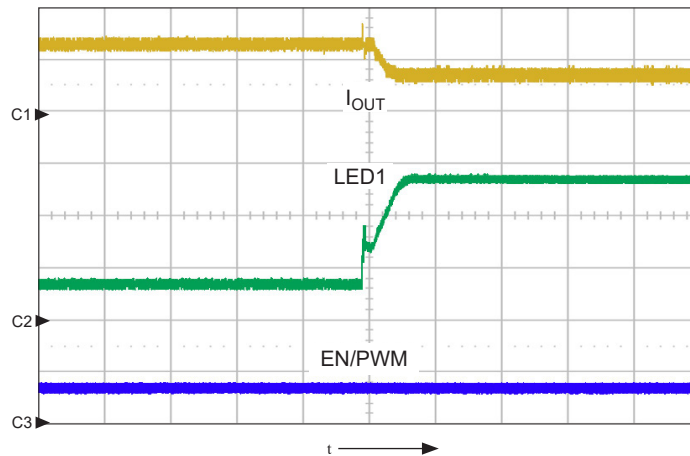


Figure 20. Example of the disabling of an LED string when the LED pin voltage is increased above 4.6 V; shows I_{OUT} (ch1, 200 mA/div.), LED1 (ch2, 5 V/div.), and EN/PWM (ch3, 5 V/div.), 10 μ s/div.

Figure 21 illustrates when the output of the A8515 is disconnected from load during normal operation. The output voltage instantly increases up to OVP voltage level and then the boost stops switching to prevent damage to the IC. If the output is drained off, eventually the boost might start switching for a short duration until the OVP threshold is hit again.

Figure 22 displays a typical OVP event caused by an open LED string. After the OVP condition is detected, the boost stops switching, and the open LED string is removed from operation. Afterwards V_{OUT} is allowed to fall, and eventually the boost will resume switching and the A8515 will resume normal operation.

A8515 also has built-in secondary overvoltage protection to protect the internal switch in the event of an open diode condi-

tion. Open Schottky diode detection is implemented by detecting overvoltage on the SW pin of the device. If voltage on the SW pin exceeds the device safe operating voltage rating, the A8515 disables and remains latched. To clear this fault, the IC must be shut down either by using the EN/PWM signal or by going below the UVLO threshold on the VIN pin. Figure 23 illustrates this. As soon as the switch node voltage (SW) exceeds 60 V, the IC shuts down. Due to small delays in the detection circuit, as well as there being no load present, the switch node voltage will rise above the trip point voltage.

Figure 24 illustrates when the A8515 is being enabled during an open diode condition. The IC goes through all of its initial LED detection and then tries to enable the boost, at which point the open diode is detected.

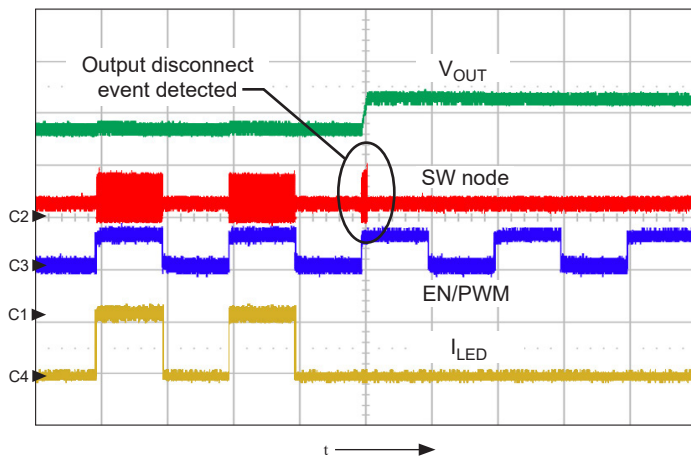


Figure 21. OVP protection in an output disconnect event; shows V_{OUT} (ch1, 10 V/div.), SW node (ch2, 50 V/div.), EN/PWM (ch3, 5 V/div.), and I_{LED} (ch4, 200 mA/div.), 1 ms/div.

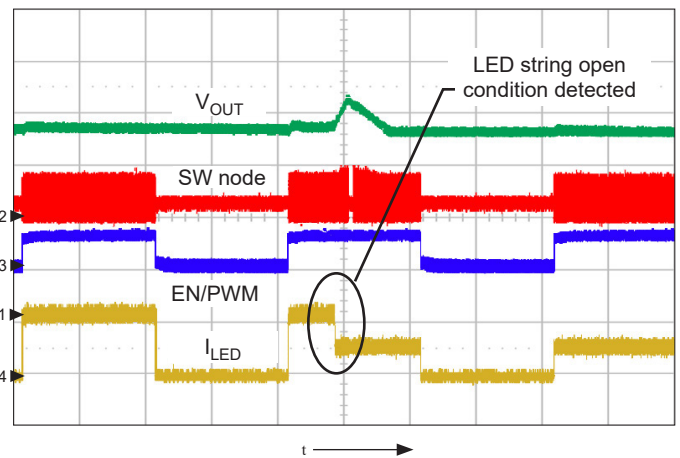


Figure 22. OVP protection in an open LED string event; shows V_{OUT} (ch1, 10 V/div.), SW node (ch2, 50 V/div.), EN/PWM (ch3, 5 V/div.), and I_{LED} (ch4, 200 mA/div.), 500 μ s/div.

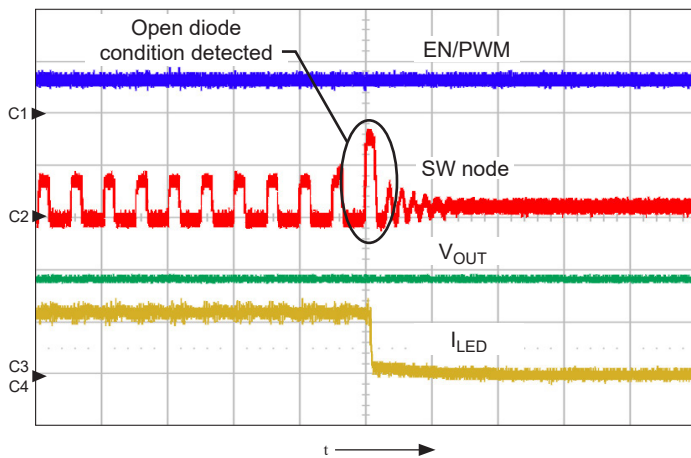


Figure 23. OVP protection in an open Schottky diode event, while the IC is in normal operation; shows EN/PWM (ch1, 5 V/div.), SW node (ch2, 50 V/div.), V_{OUT} (ch3, 20 V/div.), and I_{LED} (ch4, 200 mA/div.), 1 μ s/div.

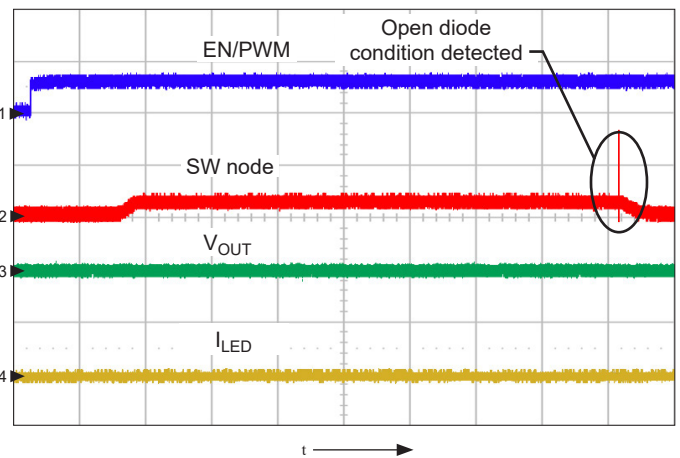


Figure 24. OVP protection when the IC is enabled during an open diode condition; shows EN/PWM (ch1, 5 V/div.), SW node (ch2, 50 V/div.), V_{OUT} (ch3, 10 V/div.), and I_{LED} (ch4, 200 mA/div.), 500 μ s/div.

BOOST SWITCH OVERCURRENT PROTECTION

The boost switch is protected with cycle-by-cycle current limiting set at a minimum of 3.0 A. There is also a secondary current limit that is sensed on the boost switch. When detected this current limit immediately shuts down the A8515. The level of this cur-

rent limit is set above the cycle-by-cycle current limit to protect the switch from destructive currents when the boost inductor is shorted. Various boost switch overcurrent conditions are shown in figures 25 through 27.

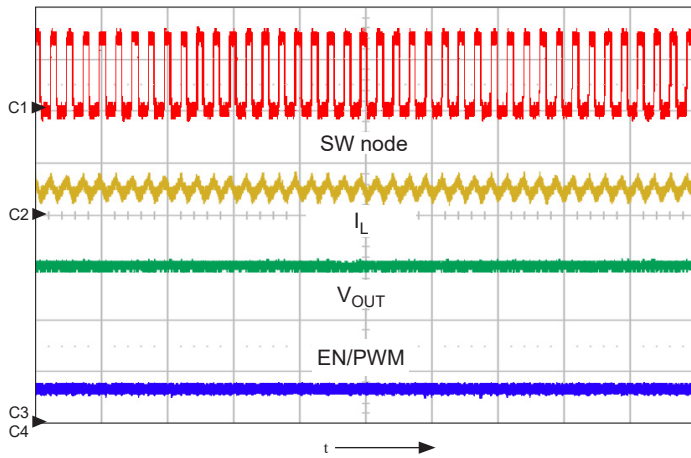


Figure 25. Normal operation of the switch node (SW); inductor current (I_L) and output voltage (V_{OUT}) for 9 series LEDs in each of 2 strings configuration; shows SW node (ch1, 20 V/div.), I_L (ch2, 1 A/div.), V_{OUT} (ch3, 10 V/div.), and EN/PWM (ch4, 5 V/div.), 2 μ s/div.

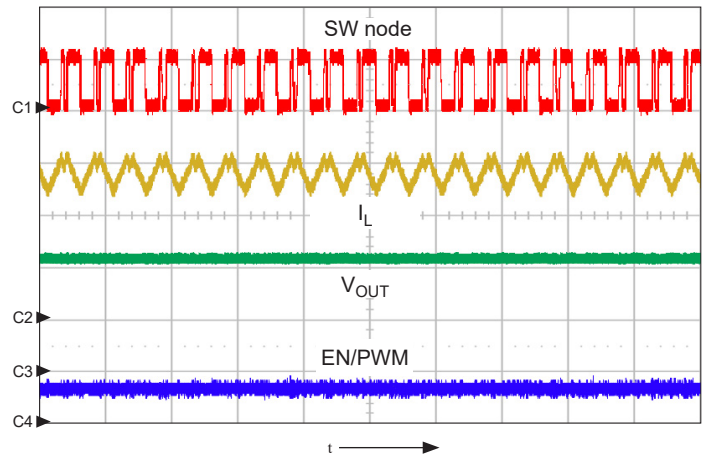


Figure 26. Cycle-by-cycle current limiting; inductor current (yellow trace, I_L), note reduction in output voltage as compared to normal operation with the same configuration (figure 25); shows SW node (ch1, 20 V/div.), I_L (ch2, 1 A/div.), V_{OUT} (ch3, 10 V/div.), and EN/PWM (ch4, 5 V/div.), 2 μ s/div.

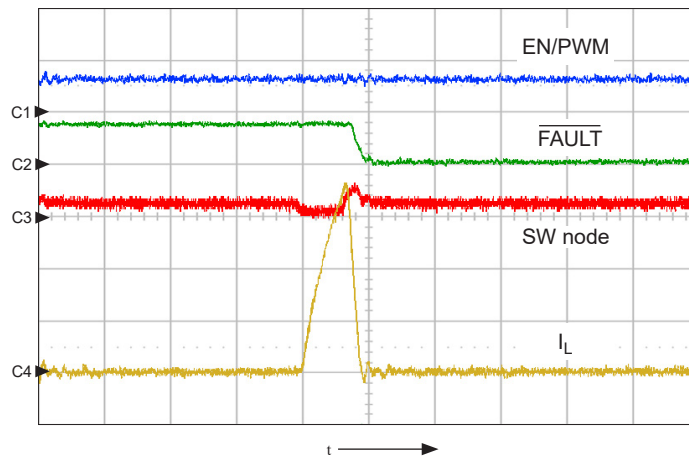


Figure 27. Secondary boost switch current limit; when this limit is hit, the A8515 immediately shuts down; shows EN/PWM (ch1, 5 V/div.), V_{OUT} (ch2, 5 V/div.), SW node (ch3, 50 V/div.), and I_L (ch4, 2 A/div.), 100 ns/div.

INPUT OVERCURRENT PROTECTION AND DISCONNECT SWITCH

The primary function of the input disconnect switch is to protect the system and the device from catastrophic input currents during a fault condition. The external circuit implementing the disconnect is shown in figure 28. If the input disconnect switch is not used, the VSENSE pin must be tied to VIN and the GATE pin must be left open.

When selecting the external PMOS, check for the following parameters:

- Drain-source breakdown voltage $V_{(BR)DSS} > -40\text{ V}$
- Gate threshold voltage (make sure it is fully conducting at $V_{GS} = -4\text{ V}$, and cut-off at -1 V)
- $R_{DS(on)}$: Make sure the on-resistance is rated at $V_{GS} = -4.5\text{ V}$ or similar, not at -10 V ; derate it for higher temperature

If the input current level goes above $V_{SENSETRIP}$ of the preset current limit threshold, the A8515 will shut down in less than $3\text{ }\mu\text{s}$ regardless of user input (see figure 29). This is a latched condition. The Fault flag is also set to indicate a fault. This feature is

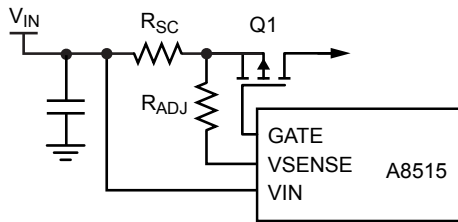


Figure 28. Typical circuit showing the implementation of the input disconnect feature.

meant to prevent catastrophic failure in the system due to a short of the inductor to GND.

SETTING THE CURRENT SENSE RESISTOR

The typical threshold for the current sense circuit is 180 mV , when R_{ADJ} is $0\text{ }\Omega$. This voltage can be trimmed by the R_{ADJ} resistor. The typical trip point should be set at about 3 A , which coincides with the cycle-by-cycle current limit minimum threshold. A sample calculation is done below:

Given: 2.85 A of input current, and the calculated maximum value of the sense resistor, $R_{SC} = 0.063\text{ }\Omega$.

The R_{SC} chosen is $0.056\text{ }\Omega$, a standard.

Also:

$$R_{ADJ} = (V_{SENSETRIP} - V_{ADJ}) / I_{ADJ} \quad (6)$$

The trip point voltage is calculated as:

$$V_{ADJ} = 2.85\text{ A} \times 0.056\text{ }\Omega = 0.160\text{ V}$$

$$R_{ADJ} = (0.180 - 0.160\text{ V}) / (20.3\text{ }\mu\text{A}) = 1.0\text{ k}\Omega$$

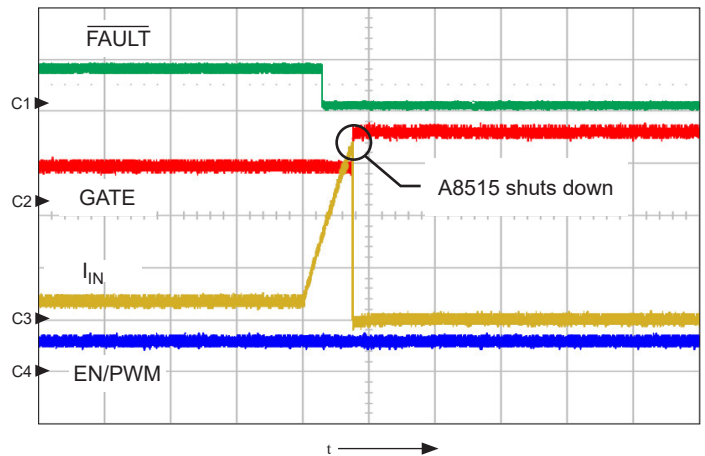


Figure 29. Typical secondary overcurrent fault condition. I_{IN} is the input current through the switch. When the current limit is reached the A8515 disables the gate of the disconnect switch (GATE); shows FAULT (ch1, 5 V/div.), GATE (ch2, 10 V/div.), I_{IN} (ch3, 2 A/div.), and EN/PWM (ch4, 5 V/div. , 5 ms/div.)

INPUT UVLO

When V_{IN} and V_{SENSE} rise above the $V_{UVLOrise}$ threshold, the A8515 is enabled. A8515 is disabled when V_{IN} falls below the $V_{UVLOfall}$ threshold for more than 50 μs . This small delay is used to avoid shutting down because of momentary glitches in the input power supply. When V_{IN} falls below 4.35 V, the IC will shut down (see figure 30).

VDD

The VDD pin provides regulated bias supply for internal circuits. Connect the capacitor C_{VDD} with a value of 0.1 μF or greater to this pin. The internal LDO can deliver no more than 2 mA of current with a typical V_{DD} of about 3.5 V, enabling this pin to serve as the pull-up voltage for the **FAULT** pin.

SHUTDOWN

If the EN/PWM pin is pulled low for more than t_{pWML} , the device enters shutdown mode and clears all internal fault registers. As an example, at a 2 MHz clock frequency, it will take approximately 16.3 ms to shut down the IC into the low power mode (figure 31). When the A8515 is shut down, the IC will dis-

able all current sources and wait until the EN/PWM signal goes high to re-enable the IC. If faster shut down is required, the FSET pin can be used.

FAULT PROTECTION DURING OPERATION

The A8515 constantly monitors the state of the system to determine if any fault conditions occur during normal operation. The response to a triggered fault condition is summarized in the Fault Mode table, on the next page.

The possible fault conditions that the device can detect are: Open LED pin, LED pin shorted to GND, shorted inductor, V_{OUT} short to GND, SW pin shorted to GND, ISET pin shorted to GND, and input disconnect switch source shorted to GND.

Note the following:

- Some of the protection features might not be active during startup, to prevent false triggering of fault conditions.
- Some of these faults will not be protected if the input disconnect switch is not being used. An example of this is V_{OUT} short to ground.

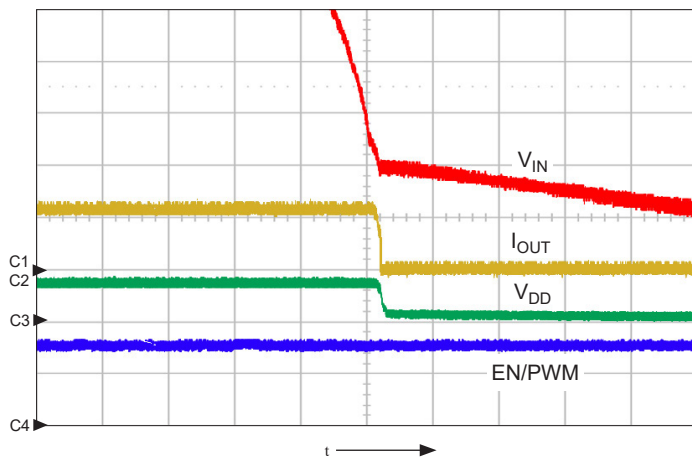


Figure 30. Shutdown showing a falling input voltage (V_{IN}); shows V_{IN} (ch1, 2 V/div.), I_{OUT} (ch2, 200 mA/div.), V_{DD} (ch3, 5 V/div.), and EN/PWM (ch4, 2 V/div.), 5 ms/div.

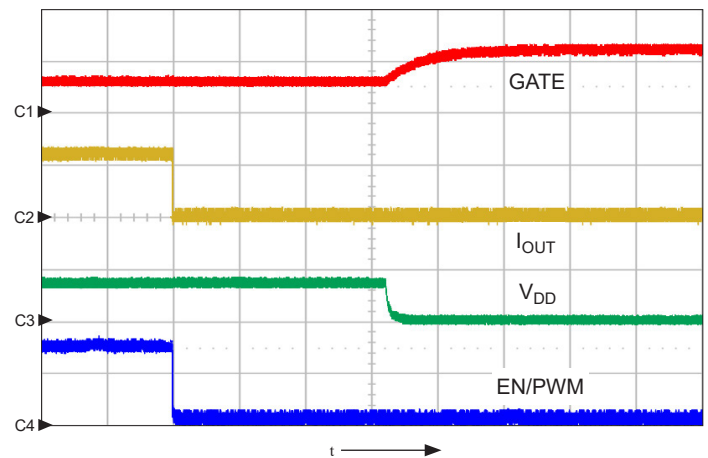


Figure 31. Shutdown using the enable function, showing the 16 ms delay between the EN/PWM signal and when the VDD and GATE of the disconnect switch turns off; shows GATE (ch1, 10 V/div.), I_{OUT} (ch2, 200 mA/div.), V_{DD} (ch3, 5 V/div.), and EN/PWM (ch4, 2 V/div.), 5 ms/div.

Fault Mode Table

Fault Name	Type	Active	Fault Flag Set	Description	Boost	Disconnect switch	Sink driver
Primary switch overcurrent protection (cycle-by-cycle current limit)	Auto-restart	Always	No	This fault condition is triggered by the cycle-by-cycle current limit, $I_{SW(LIM)}$. Prevents current in inductor from exceeding $I_{SW(LIM)}$ 3.38 A (Typical).	Off for a single cycle	On	On
Secondary switch current limit	Latched	Always	Yes	When the current through the boost switch exceeds secondary current SW limit ($I_{SW(LIM2)}$) the device immediately shuts down the disconnect switch, LED drivers, and boost. The Fault flag is set. To re-enable the device, the EN/PWM pin must be pulled low for 32750 clock cycles.	Off	Off	Off
Input disconnect current limit	Latched	Always	Yes	The device is immediately shut off if the voltage across the input sense resistor goes above $V_{SENSETRIP}$. The Fault flag is set. To re-enable the device the EN/PWM pin must be pulled low for 32750 clock cycles.	Off	Off	Off
Secondary OVP	Latched	Always	Yes	Secondary overvoltage protection is used for open diode detection. When diode D1 opens, the SW pin voltage will increase until $V_{OVP(SEC)}$ is reached. This fault latches the IC. The input disconnect switch is disabled as well as the LED drivers, and the Fault flag is set. To re-enable the part the EN/PWM pin must be pulled low for 32750 clock cycles.	Off	Off	Off
LED Pin Short Protection	Auto-restart	Startup	No	This fault prevents the device from starting-up if any of the LEDx pins are shorted. The device stops soft-start from starting while any of the LED pins are determined to be shorted. Once the short is removed, soft-start is allowed to start.	Off	On	Off
LED Pin open	Auto-restart	Normal Operation	No	When an LED pin is open the device will determine which LED pin is open by increasing the output voltage until OVP is reached. Any LED string not in regulation will be turned off. The device will then go back to normal operation by reducing the output voltage to the appropriate voltage level.	On	On	Off for open pins. On for all others.
ISET Short Protection	Auto-restart	Always	No	This fault occurs when the ISET current goes above 150% of the maximum current. The boost will stop switching and the IC will disable the LED sinks until the fault is removed. When the fault is removed the IC will try to regulate to the preset LED current.	Off	On	Off

Continued on the next page...

Fault Mode Table (continued)

Fault Name	Type	Active	Fault Flag Set	Description	Boost	Disconnect Switch	Sink driver
FSET Short Protection	Auto-restart	Always	Yes	Fault occurs when the FSET current goes above 150% of maximum current. The boost will stop switching, the disconnect switch will turn off and the IC will disable the LED sinks until the fault is removed. When the fault is removed, the IC will try to restart with soft-start.	Off	Off	Off
Overvoltage Protection	Auto-restart	Always	No	Fault occurs when OVP pin exceeds $V_{OVP(th)}$ threshold. The A8515 will immediately stop switching to try to reduce the output voltage. If the output voltage decreases, then the A8515 will restart switching to regulate the output voltage.	Stop during OVP event.	On	On
LED Short Protection	Auto-restart	Always	No	Fault occurs when the LED pin voltage exceeds 5.1 V. When the LED short protection is detected the LED string above the threshold will be removed from operation.	On	On	Off for shorted pins. On for all others.
Overtemperature Protection	Auto-restart	Always	No	Fault occurs when the die temperature exceeds the overtemperature threshold, typically 165°C.	Off	Off	Off
VIN UVLO	Auto-restart	Always	No	Fault occurs when V_{IN} drops below V_{UVLO} , typically 3.90 V. This fault resets all latched faults.	Off	Off	Off

APPLICATIONS INFORMATION

DESIGN EXAMPLE FOR BOOST CONFIGURATION

This section provides a method for selecting component values when designing an application using the A8515. The resulting design is diagramed in figure 32.

Assumptions: For the purposes of this example, the following are given as the application requirements:

- V_{BAT} : 10 to 14 V
- Quantity of LED channels, $\#_{CHANNELS}$: 2
- Quantity of series LEDs per channel, $\#_{SERIESLEDS}$: 10
- LED current per channel, I_{LED} : 120 mA
- V_f at 120 mA: 3 to 3.6 V
- f_{SW} : 2 MHz
- $T_A(\text{max})$: 65°C
- PWM dimming frequency: 200 Hz, 1% Duty cycle

Procedure: The procedure consists of selecting the appropriate configuration and then the individual component values, in an ordered sequence.

Step 1: Connect LEDs to pins LED1 and LED2.

Step 2: Determining the LED current setting resistor R_{ISET} :

$$R_{ISET} = 1.003 \times 980 / I_{LED} \quad (7)$$

$$= 983 / 120 \text{ mA} = 8.19 \text{ k}\Omega$$

Choose a 8.25 k Ω resistor.

Step 3: Determining the OVP resistor. The OVP resistor is connected between the OVP pin and the output voltage of the converter.

Step 3a: The first step is determining the maximum voltage based on the LED requirements. Then this value and the regulation voltage (V_{LED}) should be added together, as well as another 2 V to take noise and output ripple into consideration. The V_{LED} of the A8515 is 720 mV.

$$V_{OUT(OVP)} = \#_{SERIESLEDS} \times V_f + V_{LED} + 2 \quad (8)$$

$$= 10 \times 3.6 \text{ V} + 2.0 \text{ V} + 0.720 \text{ V}$$

$$= 38.72 \text{ V}$$

Then the OVP resistor is:

$$R_{OVP} = (V_{OUT(OVP)} - V_{OVP(th)}) / I_{OVPH} \quad (9)$$

$$= (38.72 \text{ V} - 8.1 \text{ V}) / 199 \text{ }\mu\text{A} = 154 \text{ k}\Omega$$

where both I_{OVPH} and $V_{OVP(th)}$ are taken from the Electrical Characteristics table.

Chose a value of resistor that is higher value than the calculated R_{OVP} . In this case a value of 158 k Ω was selected. Below is the actual value of the minimum OVP trip level with the selected resistor:

$$V_{OUT(OVP)} = 158 \text{ k}\Omega \times 199 \text{ }\mu\text{A} + 8.1 \text{ V} = 39.5 \text{ V}$$

Step 3b: At this point a quick check must be done to see if the conversion ratio is acceptable for the selected frequency.

$$D_{\text{maxofboost}} = 1 - t_{\text{SWOFFTIME}} \times f_{\text{SW}} \quad (10)$$

$$= 1 - 1.5 \times 47 \text{ ns} \times 2 \text{ MHz} = 85.9\%$$

where minimum off time ($t_{\text{SWOFFTIME}}$) is found in the Electrical Characteristics table.

The Theoretical Maximum V_{OUT} is then calculated as:

$$V_{OUT\text{the(max)}} = \frac{V_{IN(\text{min})}}{1 - D_{\text{maxofboost}}} - V_d \quad (11)$$

$$= \frac{10 \text{ V}}{1 - 0.859} - 0.4 = 70.5 \text{ V}$$

where V_d is the diode forward voltage. A good approximation of efficiency η can be taken from the efficiency curves located in this datasheet. A value of 90% is a good starting approximation.

The Theoretical Maximum V_{OUT} value must be greater than the value $V_{OUT(OVP)}$. If this is not the case, the switching frequency of the boost converter must be reduced to meet the maximum duty cycle requirements.

Step 4: Selecting the inductor. The inductor must be chosen such that it can handle the necessary input current. In most applications, due to stringent EMI requirements, the system must operate in continuous conduction mode throughout the whole input voltage range.

Step 4a: Determining the duty cycle, calculated as follows:

$$D(\max) = 1 - \frac{V_{IN}(\min)}{V_{OUT(OVP)} + V_d} \quad (12)$$

$$= 1 - \frac{10 \text{ V}}{39.5 + 0.4} = 74.9\%$$

Step 4b: Determining the maximum and minimum input current to the system. The minimum input current will dictate the inductor value. The maximum current rating will dictate the current rating of the inductor. First, the maximum input current, given:

$$I_{OUT} = \#_{\text{CHANNELS}} \times I_{LED} \quad (13)$$

$$= 2 \times 0.120 \text{ A} = 0.240 \text{ A}$$

then:

$$I_{IN}(\max) = \frac{V_{OUT(OVP)} \times I_{OUT}}{V_{IN}(\min) \times \eta} \quad (14)$$

$$= \frac{39.5 \text{ V} \times 240 \text{ mA}}{10 \text{ V} \times 0.9} = 1.053 \text{ A}$$

where η is efficiency.

Next, calculate minimum input current, as follows:

$$I_{IN}(\min) = \frac{V_{OUT(OVP)} \times I_{OUT}}{V_{IN}(\max) \times \eta} \quad (15)$$

$$= \frac{39.5 \text{ V} \times 240 \text{ mA}}{14 \text{ V} \times 0.9} = 0.752 \text{ A}$$

A good approximation of efficiency, η , can be taken from the efficiency curves located in the diode datasheet. A value of 90% is a good starting approximation.

Step 4c: Determining the inductor value. To ensure that the inductor operates in continuous conduction mode, the value of the inductor must be set such that the $\frac{1}{2}$ inductor ripple current is not greater than the average minimum input current. A first pass assumes I_{ripple} to be 40% of the maximum inductor current:

$$\Delta I_L = I_{IN}(\max) \times 0.4 \quad (16)$$

$$= 1.05 \text{ A} \times 0.4 = 0.42 \text{ A}$$

then:

$$L = \frac{V_{IN}(\min)}{\Delta I_L \times f_{SW}} \times D(\max) \quad (17)$$

$$= \frac{10 \text{ V}}{0.42 \text{ A} \times 2 \text{ MHz}} \times 0.749 = 8.9 \mu\text{H}$$

Step 4d: Double-check to make sure the $\frac{1}{2}$ current ripple is less than $I_{IN}(\min)$:

$$I_{IN}(\min) > \frac{1}{2} \Delta I_L \quad (18)$$

$$0.75 \text{ A} > 0.21 \text{ A}$$

A good inductor value to use would be 10 μH .

Step 4e: This step is used to verify that there is sufficient slope compensation for the inductor chosen. The slope compensation value is determined by the following formula:

$$\text{Slope Compensation} = \frac{3.6 \times f_{SW}}{2 \times 10^6} = 3.6 \text{ A}/\mu\text{s} \quad (19)$$

Next insert the inductor value used in the design:

$$\Delta I_{Lused} = \frac{V_{IN}(\min) \times D(\max)}{L_{used} \times f_{SW}} \quad (20)$$

$$= \frac{10 \text{ (V)} \times 0.75}{10 \text{ (}\mu\text{H)} \times 2.0 \text{ (MHz)}} = 0.37 \text{ A}$$

Calculate the minimum required slope:

$$\text{Required Slope (min)} = \frac{\Delta I_{Lused} \times 1 \times 10^{-6}}{\frac{1}{f_{SW}} \times (1 - D(\max))} \quad (21)$$

$$= \frac{0.37 \text{ (A)} \times 1 \times 10^{-6}}{\frac{1}{2.0 \text{ (MHz)}} \times (1 - 0.75)} = 2.97 \text{ A}/\mu\text{s}$$

If the minimum required slope is greater than the calculated slope compensation, the inductor value must be increased.

Note: The slope compensation value is in $\text{A}/\mu\text{s}$, and 1×10^{-6} is a constant multiplier.

Step 4f: Determining the inductor current rating. The inductor current rating must be greater than the $I_{IN}(\max)$ value plus the ripple current ΔI_L , calculated as follows:

$$I_L(\max) = I_{IN}(\max) + \frac{1}{2} \Delta I_{Lused} \quad (22)$$

$$= 1.05 \text{ A} + 0.37 \text{ A} / 2 = 1.24 \text{ A}$$

Step 5: Determining the resistor value for a particular switching frequency. Use the R_{FSET} values shown in figure 7. For example, a 10 k Ω resistor will result in a 2 MHz switching frequency.

Step 6: Choosing the proper switching diode. The switching diode must be chosen for three characteristics when it is used in

LED lighting circuitry. The most obvious two are: current rating of the diode and reverse voltage rating.

The reverse voltage rating should be such that during operation condition, the voltage rating of the device is larger than the maximum output voltage. In this case it is $V_{OUT(OVP)}$.

The peak current through the diode is calculated as:

$$I_{dp} = I_{IN(max)} + \frac{1}{2} \Delta I_{Lused} \quad (23)$$

$$= 1.05 \text{ A} + 0.37 \text{ A} / 2 = 1.24 \text{ A}$$

The third major component in deciding the switching diode is the reverse current, I_R , characteristic of the diode. This characteristic is especially important when PWM dimming is implemented. During PWM off-time the boost converter is not switching. This results in a slow bleeding off of the output voltage, due to leakage currents. I_R can be a large contributor, especially at high temperatures. On the diode that was selected in this design, the current varies between 1 and 100 μA .

Step 7: Choosing the output capacitors. The output capacitors must be chosen such that they can provide filtering for both the boost converter and for the PWM dimming function. The biggest factors that contribute to the size of the output capacitor are: PWM dimming frequency, and PWM duty cycle. Another major contributor is leakage current (I_{LK}). This current is the combination of the OVP leakage current as well as the reverse current of the switching diode. In this design the PWM dimming frequency is 200 Hz and the minimum duty cycle is 1%. Typically, the voltage variation on the output (V_{COUT}) during PWM dimming must be less than 250 mV, so that no audible hum can be heard. The capacitance can be calculated as follows:

$$C_{OUT} = I_{LK} \times \frac{1 - D(\min)}{f_{PWM(\text{dimming})} \times V_{COUT}} \quad (24)$$

$$= 200 \mu\text{A} \times \frac{1 - 0.01}{200 \text{ Hz} \times 0.250 \text{ V}} = 3.96 \mu\text{F}$$

A capacitor larger than 3.96 μF should be selected due to degradation of capacitance at high voltages on the capacitor. A ceramic

4.7 μF 50 V capacitor is a good choice to fulfill this requirement.

Corresponding capacitors include:

Vendor	Value	Part number
Murata	4.7 μF 50 V	GRM32ER71H475KA88L
Murata	2.2 μF 50 V	GRM31CR71H225KA88L

The rms current through the capacitor is given by:

$$I_{COUT(rms)} = I_{OUT} \sqrt{\frac{D(\max) + \frac{\Delta I_{Lused}}{I_{IN(max)} \times 12}}{1 - D(\max)}} \quad (25)$$

$$= 0.240 \text{ A} \sqrt{\frac{0.75 + \frac{0.37}{1.05 \times 12}}{1 - 0.75}} = 0.42 \text{ A}$$

The output capacitor must have a current rating of at least 420 mA. The capacitor selected in this design was a 4.7 μF 50 V capacitor with a 1.5 A current rating.

Step 8: Selecting input capacitor. The input capacitor must be selected such that it provides a good filtering of the input voltage waveform. A good rule of thumb is to set the input voltage ripple ΔV_{IN} to be 1% of the minimum input voltage. The minimum input capacitor requirements are as follows:

$$C_{IN} = \frac{\Delta I_{Lused}}{8 \times f_{SW} \times \Delta V_{IN}} \quad (26)$$

$$= \frac{0.37 \text{ A}}{8 \times 2 \text{ MHz} \times 0.1 \text{ V}} = 0.23 \mu\text{F}$$

The rms current through the capacitor is given by:

$$I_{IN,rms} = \frac{I_{OUT} \times \frac{\Delta I_{L,used}}{I_{IN(max)}}}{(1 - D(max)) \sqrt{12}} \quad (27)$$

$$= \frac{0.240 \times \frac{0.37}{1.05}}{(1 - 0.75) \sqrt{12}} = 0.10 \text{ A}$$

A good ceramic input capacitor with ratings of 2.2 μF 50V or 4.7 μF 50 V will suffice for this application. Corresponding capacitors include:

Vendor	Value	Part number
Murata	4.7 μF 50 V	GRM32ER71H475KA88L
Murata	2.2 μF 50 V	GRM31CR71H225KA88L

Step 9: Choosing the input disconnect switch components. Set the input disconnect current limit to 3 A by choosing a sense resistor. The calculated maximum value of the sense resistor is:

$$R_{SC(max)} = V_{SENSEtrip} / 3.0 \text{ A} \quad (28)$$

$$= 0.180 \text{ V} / 3.0 \text{ A} = 0.060 \Omega$$

The R_{SC} chosen is 0.056 Ω , a standard value.

The trip point voltage must be:

$$V_{ADJ} = 3.0 \text{ A} \times 0.056 \Omega = 0.168 \text{ V}$$

$$R_{ADJ} = (V_{SENSEtrip} - V_{ADJ}) / I_{ADJ} \quad (29)$$

$$R_{ADJ} = (0.180 \text{ V} - 0.168 \text{ V}) / 20.3 \mu\text{A} = 591 \Omega$$

A value of 590 Ω was selected for this design.

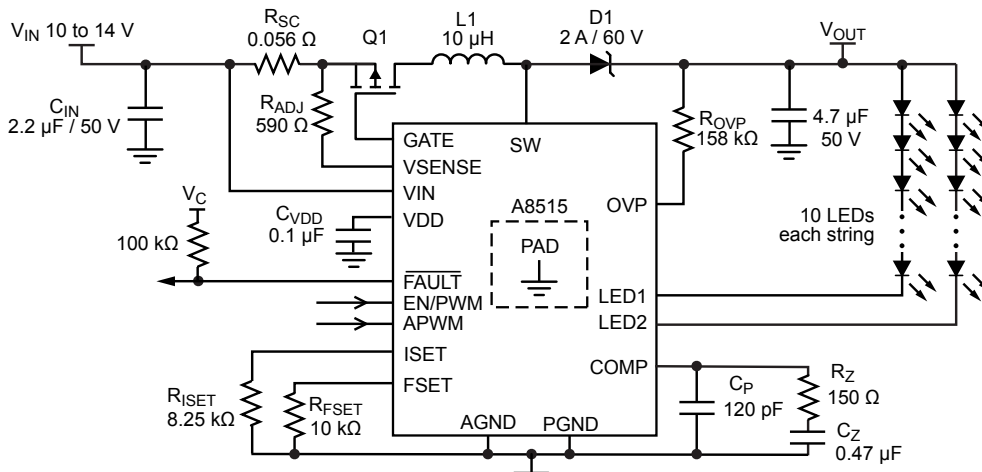


Figure 32. The schematic diagram showing calculated values from the design example above

Design Example for SEPIC Configuration

This section provides a method for selecting component values when designing an application using the A8515 in SEPIC (Single-Ended Primary-Inductor Converter) circuit. SEPIC topology has the advantage that it can generate a positive output voltage either higher or lower than the input voltage. The resulting design is diagrammed in figure 33.

Assumptions: For the purposes of this example, the following are given as the application requirements:

- V_{BAT} : 6 to 14 V ($V_{IN(min)}$: 5 V and $V_{IN(max)}$: 16 V)
- Quantity of LED channels, $\#_{CHANNELS}$: 2
- Quantity of series LEDs per channel, $\#_{SERIESLEDS}$: 4
- LED current per channel, I_{LED} : 120 mA
- LED V_f at 120 mA: ≈ 3.3 V
- f_{SW} : 2 MHz
- $T_A(max)$: 65°C
- PWM dimming frequency: 200 Hz, 1% duty cycle

Procedure: The procedure consists of selecting the appropriate configuration and then the individual component values, in an ordered sequence.

Step 1: Connect LEDs to pins LED1 and LED2. If only one of the LED channels is needed, the unused LEDx pin should be pulled to ground using a 1.5 k Ω resistor.

Step 2: Determining the LED current setting resistor R_{ISET} :

$$R_{ISET} = (V_{ISET} \times A_{ISET}) / I_{LED} \quad (30)$$

$$= (1.003 \text{ (V)} \times 980) / 0.120 \text{ (A)} = 8.19 \text{ k}\Omega$$

Choose an 8.25 k Ω 1% resistor (or 16.2 k Ω if LED current is 60 mA/channel).

Step 3: Determining the OVP resistor. The OVP resistor is connected between the OVP pin and the output voltage of the converter.

Step 3a: The first step is determining the maximum voltage based on the LED requirements. The regulation voltage, V_{LED} ,

of the A8515 is 720 mV. A constant term, 2 V, is added to give margin to the design due to noise and output voltage ripple.

$$V_{OUT(OVP)} = \#_{SERIESLEDS} \times V_f + V_{LED} + 2 \text{ (V)} \quad (31)$$

$$= 4 \times 3.3 \text{ (V)} + 0.72 \text{ (V)} + 2 \text{ (V)} = 15.9 \text{ V}$$

Then the OVP resistor is:

$$R_{OVP} = (V_{OUT(OVP)} - V_{OVP(th)}) / I_{OVPH} \quad (32)$$

$$= (15.9 \text{ (V)} - 8.1 \text{ (V)}) / 0.199 \text{ (mA)} = 39.196 \text{ k}\Omega$$

where both I_{OVPH} and $V_{OVP(th)}$ are taken from the Electrical Characteristics table.

In this case a value of 39.2 k Ω was selected. Below is the actual value of the minimum OVP trip level with the selected resistor:

$$V_{OUT(OVP)} = 39.2 \text{ (k}\Omega) \times 0.199 \text{ (mA)} + 8.1 \text{ (V)} = 15.9 \text{ V}$$

Step 3b: At this point a quick check must be done to determine if the conversion ratio is acceptable for the selected frequency.

$$D_{max} = 1 - t_{SWOFFTIME} \times f_{SW} \quad (33)$$

$$= 1 - 1.5 \times 47 \text{ (ns)} \times 2 \text{ (MHz)} = 85.9\%$$

where the minimum off-time ($t_{SWOFFTIME}$) is found in the Electrical Characteristics table.

The Theoretical Maximum V_{OUT} is then calculated as:

$$V_{OUT(max)} = V_{IN(min)} \times \frac{D_{max}}{1 - D_{max}} - V_d \quad (34)$$

$$= 5 \text{ (V)} \times \frac{0.86}{1 - 0.86} - 0.4 \text{ (V)} = 30.3 \text{ V}$$

where V_d is the diode forward voltage.

The Theoretical Maximum V_{OUT} value must be greater than the value $V_{OUT(OVP)}$. If this is not the case, it may be necessary to reduce the frequency to allow the boost to convert the voltage ratios.

Step 4: Selecting the inductor. The inductor must be chosen such that it can handle the necessary input current. In most applica-

tions, due to stringent EMI requirements, the system must operate in continuous conduction mode throughout the whole input voltage range.

Step 4a: Determining the duty cycle, calculated as follows:

$$D(\max) = \frac{V_{\text{OUT(OVP)}} + V_d}{V_{\text{IN(min)}} + V_{\text{OUT(OVP)}} + V_d} \quad (35)$$

$$= \frac{15.9 \text{ (V)} + 0.4 \text{ (V)}}{5 \text{ (V)} + 15.9 \text{ (V)} + 0.4 \text{ (V)}} = 76.5\%$$

Step 4b: Determining the maximum and minimum input current to the system. The minimum input current will dictate the inductor value. The maximum current rating will dictate the current rating of the inductor. First, the maximum input current, given:

$$I_{\text{OUT}} = \#_{\text{CHANNELS}} \times I_{\text{LED}} \quad (36)$$

$$= 2 \times 120 \text{ (mA)} = 0.240 \text{ A}$$

then:

$$I_{\text{IN(max)}} = \frac{V_{\text{OUT(OVP)}} \times I_{\text{OUT}}}{V_{\text{IN(min)}} \times \eta} \quad (37)$$

$$= \frac{15.9 \text{ (V)} \times 0.24 \text{ (A)}}{5 \text{ (V)} \times 0.90} = 0.848 \text{ A}$$

where η is efficiency.

Next, calculate minimum input current, as follows:

$$I_{\text{IN(min)}} = \frac{V_{\text{OUT(OVP)}} \times I_{\text{OUT}}}{V_{\text{IN(max)}} \times \eta} \quad (38)$$

$$= \frac{15.9 \text{ (V)} \times 0.24 \text{ (A)}}{16 \text{ (V)} \times 0.90} = 0.265 \text{ A}$$

Step 4c: Determining the inductor value. To ensure that the inductor operates in continuous conduction mode, the value of the inductor must be set such that the $\frac{1}{2}$ inductor ripple current is not greater than the average minimum input current. As a first pass assume I_{ripple} to be 30% of the maximum inductor current:

$$\Delta I_L = I_{\text{IN(max)}} \times I_{\text{ripple}} \quad (39)$$

$$= 0.848 \times 0.30 = 0.254 \text{ A}$$

then:

$$L = \frac{V_{\text{IN(min)}}}{\Delta I_L \times f_{\text{SW}}} \times D(\max) \quad (40)$$

$$= \frac{5 \text{ (V)}}{0.254 \text{ (A)} \times 2 \text{ (MHz)}} \times 0.765 = 7.53 \text{ } \mu\text{H}$$

Step 4d: Double-check to make sure the $\frac{1}{2}$ current ripple is less than $I_{\text{IN(min)}}$:

$$I_{\text{IN(min)}} > \frac{1}{2} \Delta I_L \quad (41)$$

$$0.265 \text{ A} > 0.127 \text{ A}$$

A good inductor value to use would be 10 μH .

Step 4e: Next insert the inductor value used in the design to determine the actual inductor ripple current:

$$\Delta I_{\text{Lused}} = \frac{V_{\text{IN(min)}} \times D(\max)}{L_{\text{used}} \times f_{\text{SW}}} \quad (42)$$

$$= \frac{5 \text{ (V)} \times 0.765}{10 \text{ (}\mu\text{H)} \times 2 \text{ (MHz)}} = 0.191 \text{ A}$$

Step 4f: Determining the inductor current rating. The inductor current rating must be greater than the $I_{\text{IN(max)}}$ value plus half of the ripple current ΔI_L , calculated as follows:

$$L(\min) = I_{\text{IN(max)}} + \frac{1}{2} \Delta I_{\text{Lused}} \quad (43)$$

$$= 0.848 \text{ (A)} + 0.096 \text{ (A)} = 0.944 \text{ A}$$

Step 5: Determining the resistor value for a particular switching frequency. Use the R_{FSET} values shown in figure 6. For example, a 10 k Ω resistor will result in an 2 MHz switching frequency.

Step 6: Choosing the proper switching diode. The switching diode must be chosen for three characteristics when it is used in LED lighting circuitry. The most obvious two are: current rating of the diode and reverse voltage rating.

The reverse breakdown voltage rating for the output diode in a SEPIC circuit should be:

$$V_{BD} > V_{OUT(OVP)(max)} + V_{IN(max)} \quad (44)$$

$$> 15.9 \text{ (V)} + 16 \text{ (V)} = 31.9 \text{ V}$$

because the maximum output voltage in this case is $V_{OUT(OVP)}$.

The peak current through the diode is calculated as:

$$I_{dp} = I_{IN(max)} + \frac{1}{2} \Delta I_{Lused} \quad (45)$$

$$= 0.848 \text{ (A)} + 0.096 \text{ (A)} = 0.944 \text{ A}$$

The third major component in deciding the switching diode is the reverse current, I_R , characteristic of the diode. This characteristic is especially important when PWM dimming is implemented. During PWM off-time the boost converter is not switching. This results in a slow bleeding off of the output voltage, due to leakage currents. I_R can be a large contributor, especially at high temperatures. On the diode that was selected in this design, the current varies between 1 and 100 μA . It is often advantageous to pick a diode with a much higher breakdown voltage, just to reduce the reverse current. Therefore, for this example, pick a diode rated for a V_{BD} of 60 V, instead of just 40 V.

Step 7: Choosing the output capacitors. The output capacitors must be chosen such that they can provide filtering for both the boost converter and for the PWM dimming function. The biggest factors that contribute to the size of the output capacitor are: PWM dimming frequency and PWM duty cycle. Another major contributor is leakage current, I_{LK} . This current is the combination of the OVP leakage current as well as the reverse current of the switching diode. In this design, the PWM dimming frequency is 200 Hz and the minimum duty cycle is 1%. Typically, the voltage variation on the output, V_{COUT} , during PWM dimming must be less than 250 mV, so that no audible hum can be heard. The capacitance can be calculated as follows:

$$C_{OUT} = I_{LK} \times \frac{1 - D(\min)}{f_{PWM(dimming)} \times V_{COUT}} \quad (46)$$

$$= 200 \text{ (}\mu\text{A)} \times \frac{1 - 0.01}{200 \text{ (Hz)} \times 0.250 \text{ (V)}} = 3.96 \text{ }\mu\text{F}$$

A capacitor larger than 3.96 μF should be selected due to degradation of capacitance at high voltages on the capacitor. Select a 4.7 μF capacitor for this application.

The rms current through the capacitor is given by:

$$I_{COUTrms} = I_{OUT} \sqrt{\frac{D(\max)}{1 - D(\max)}} \quad (47)$$

$$= 0.240 \text{ (A)} \sqrt{\frac{0.765}{1 - 0.765}} = 0.433 \text{ A}$$

The output capacitor must have a ripple current rating of at least 500 mA. The capacitor selected for this design is a 4.7 μF 50 V capacitor with a 1.5 A current rating.

Step 8: Selecting input capacitor. The input capacitor must be selected such that it provides a good filtering of the input voltage waveform. A estimation rule is to set the input voltage ripple, ΔV_{IN} , to be 1% of the minimum input voltage. The minimum input capacitor requirements are as follows:

$$C_{IN} = \frac{\Delta I_{Lused}}{8 \times f_{SW} \times \Delta V_{IN}} \quad (48)$$

$$= \frac{0.191 \text{ (A)}}{8 \times 2 \text{ (MHz)} \times 0.05 \text{ (V)}} = 0.24 \text{ }\mu\text{F}$$

The rms current through the capacitor is given by:

$$C_{INrms} = \frac{\Delta I_{Lused}}{\sqrt{12}} \quad (49)$$

$$= \frac{0.191 \text{ (A)}}{\sqrt{12}} = 0.055 \text{ A}$$

A good ceramic input capacitor with a rating of 2.2 μF 25 V will suffice for this application.

Step 9: Selecting coupling capacitor C_{SW} . The minimum capacitance of C_{SW} is related to the maximum voltage ripple allowed across it:

$$C_{SW} = \frac{I_{OUT} \times D_{MAX}}{\Delta V_{SW} \times f_{SW}} \quad (50)$$

$$= \frac{0.24 \text{ (A)} \times 0.765}{0.1 \text{ (V)} \times 2 \text{ (MHz)}} = 0.92 \mu\text{F}$$

The rms current requirement of the coupling capacitor is given by:

$$I_{CSW\text{rms}} = I_{IN(\text{max})} \sqrt{\frac{1 - D(\text{max})}{D(\text{max})}} \quad (51)$$

$$= 0.848 \text{ (A)} \sqrt{\frac{1 - 0.765}{0.765}} = 0.47 \text{ A}$$

The voltage rating of the coupling capacitor must be greater than $V_{IN(\text{max})}$, or 16 V in this case. A ceramic capacitor rated for 2.2 μF 25 V will suffice for this application.

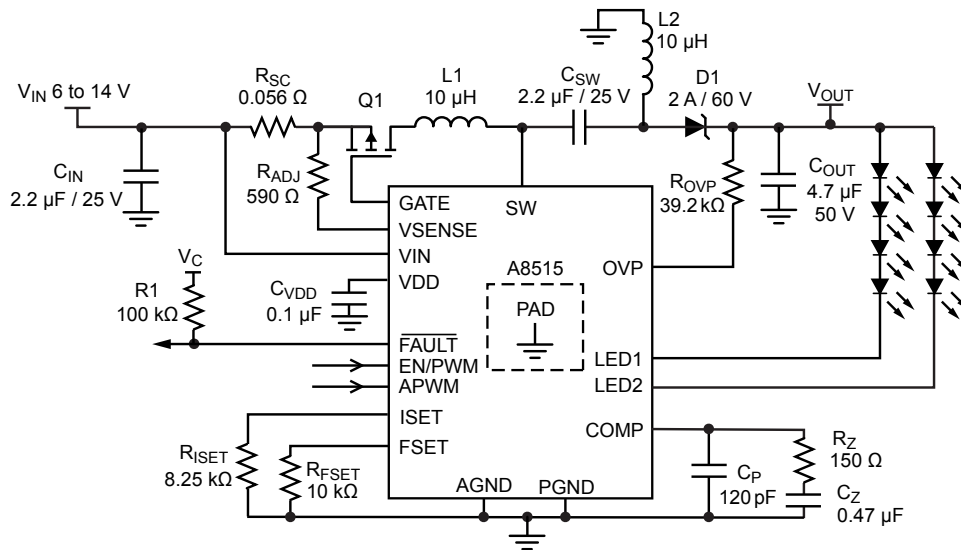


Figure 33. Typical application showing SEPIC configuration, with accurate input current sense, and VSENSE to GND protection

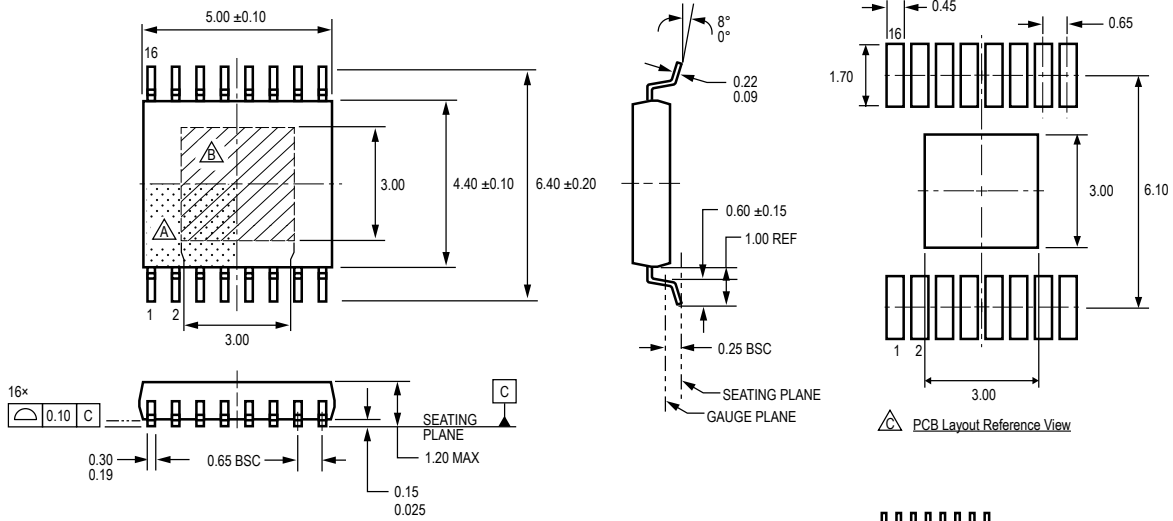
Package LP, 16-Pin TSSOP with Exposed Thermal Pad

For Reference Only – Not for Tooling Use

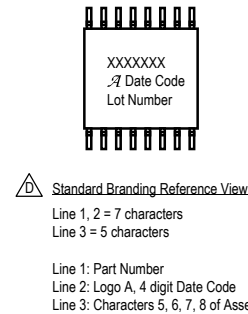
(Reference JEDEC MO-153 ABT; Allegro DWG-0000379, Rev. 3)

Dimensions in millimeters – NOT TO SCALE

Dimensions exclusive of mold flash, gate burrs, and dambar protrusions
Exact case and lead configuration at supplier discretion within limits shown



- △ Terminal #1 mark area
- △ Exposed thermal pad (bottom surface)
- △ Reference land pattern layout (reference IPC7351 SOP65P640X110-17M);
All pads a minimum of 0.20 mm from all adjacent pads; adjust as necessary to meet application process requirements and PCB layout tolerances; when mounting on a multilayer PCB, thermal vias at the exposed thermal pad land can improve thermal dissipation (reference EIA/JEDEC Standard JESD51-5)
- △ Branding scale and appearance at supplier discretion



Revision History

Number	Date	Description
2	December 15, 2011	Update to application examples, add V_{SYNC}
3	March 1, 2017	Corrected SYNC Input Logic Voltage values on page 6
4	March 28, 2019	Minor editorial updates
5	April 9, 2020	Minor editorial updates
6	April 13, 2022	Updated package drawing (page 33)

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